

IFAST – 3rd annual meeting
1.3 GHz Cavity Deposition facility progress at
UKRI

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16th - 19th April 2024



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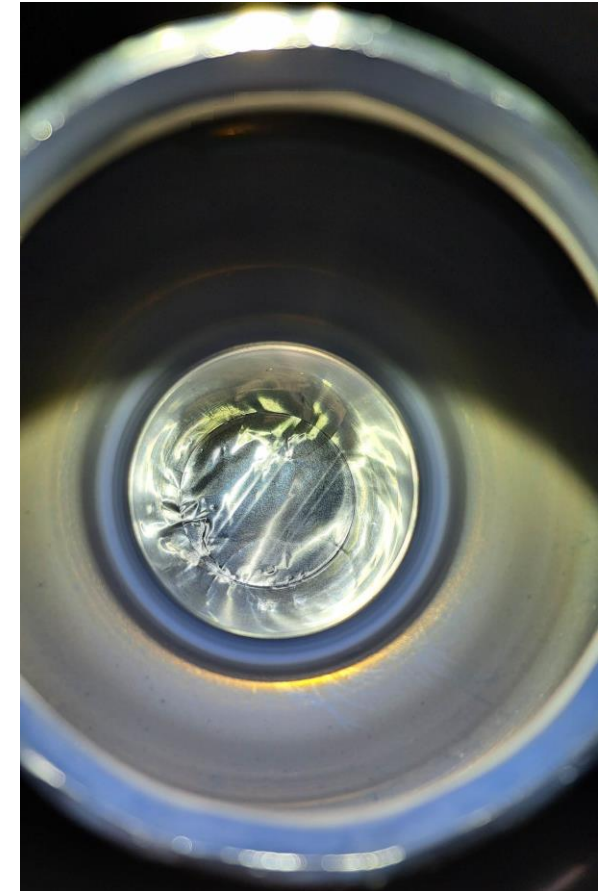


Overview

- Coating activities
 - Modified 1.3 GHz cavity - JEFF
 - Preparation for 1.3 GHz cavity - DIVERS
 - Disk samples - JEFF
- Investigation of NbN using HiPIMS and bipolar HiPIMS
 - Mass and energy analysis of the plasma phase
 - Optical emission spectroscopy

Coating activities - Modified 1.3 GHz cavity

- Deposition of Nb using bipolar HiPIMS on a modified 1.3GHz cavity.
- Initial parameters
 - Chamber filled with Kr at 6×10^{-3} mbar
 - Bipolar HiPIMS
 - U_{neg} 380 V / 800 mA / 10 A / 300 W
 - neg PW 100 us / Freq 1000Hz
 - U_{pos} 50 V / pos PW 200 us / pos delay 1.5 us
 - Deposition for 6h



No significant variation in pressure or power during the deposition



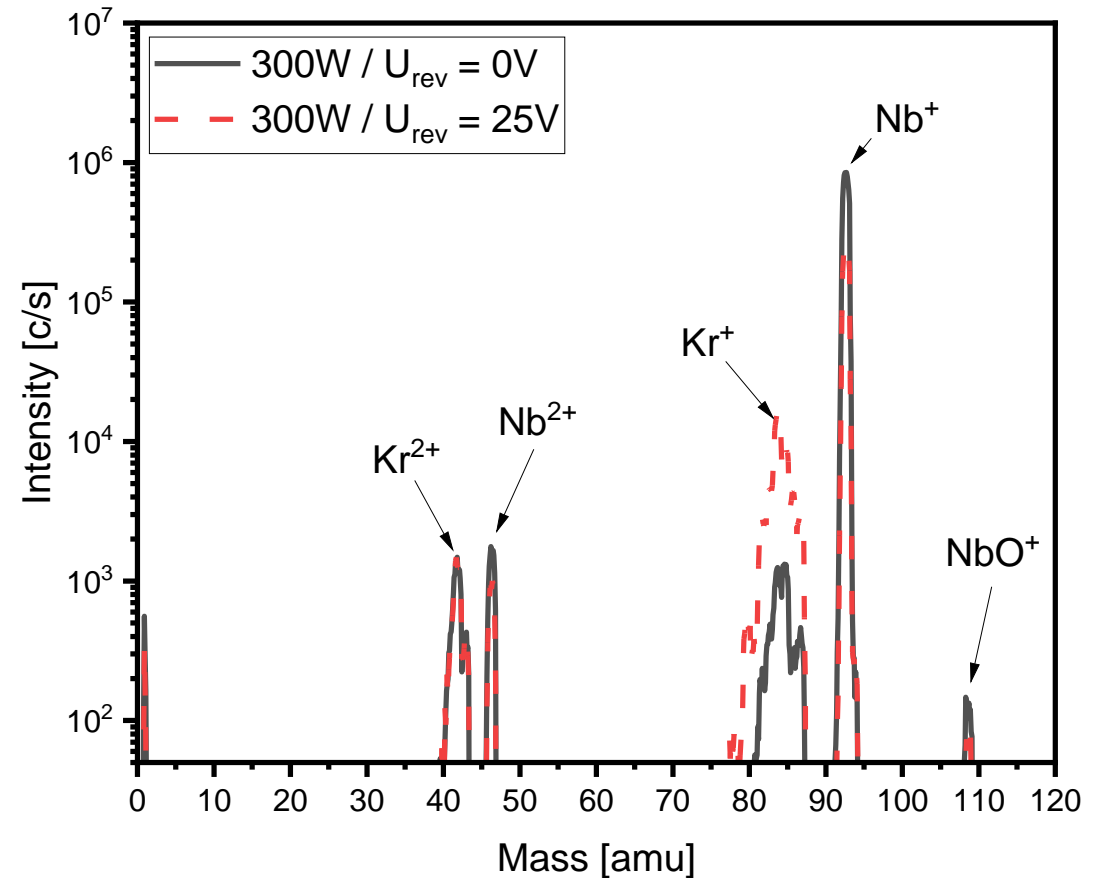
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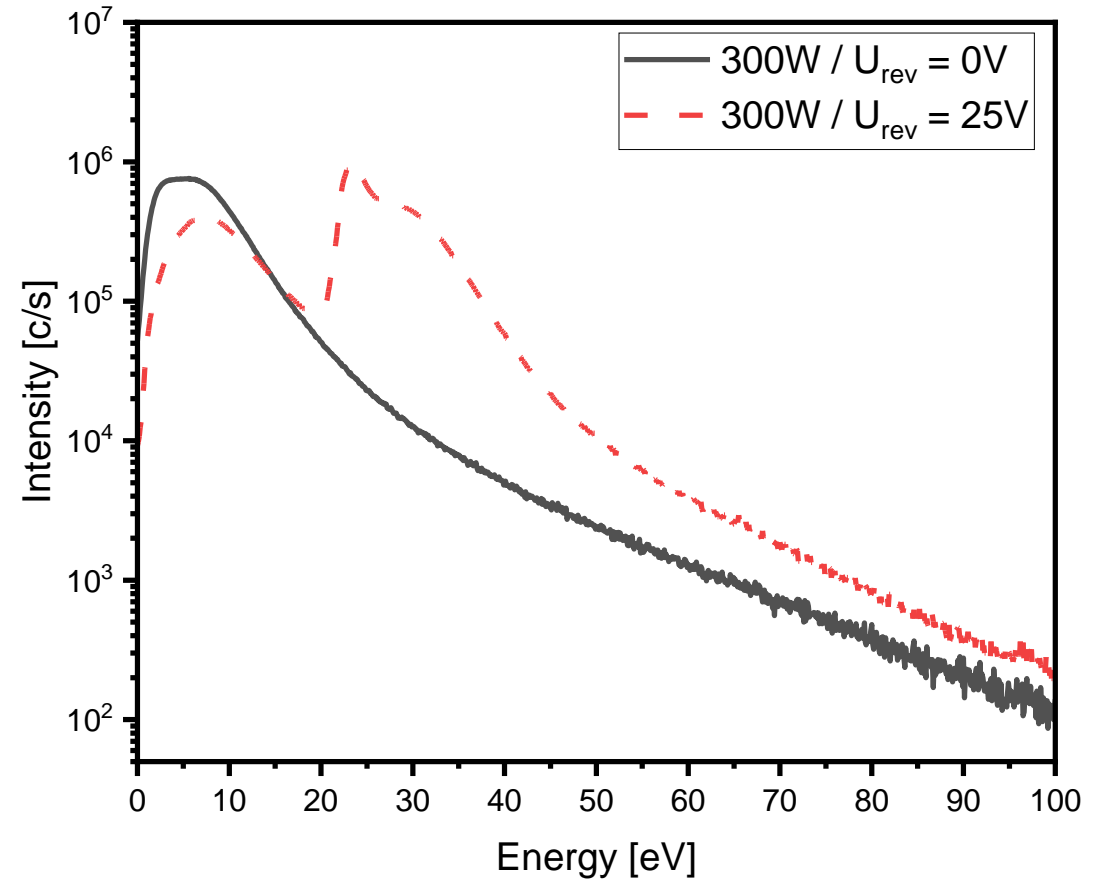
Coating activities – Modified 1.3 GHz cavity

- Mass analysis of the positive ions in bipolar HiPIMS
 - Main ions: Nb^+ (93 amu), Kr^+ (84 amu), Nb^{2+} (46 amu), Kr^{2+} (42 amu), NbO^+ (109 amu)
 - Formation of NbO^+ due by recombination with residual H_2O
 - In bipolar mode, Kr intensity increases where Nb intensity decreases. Double charged ions remain stable.



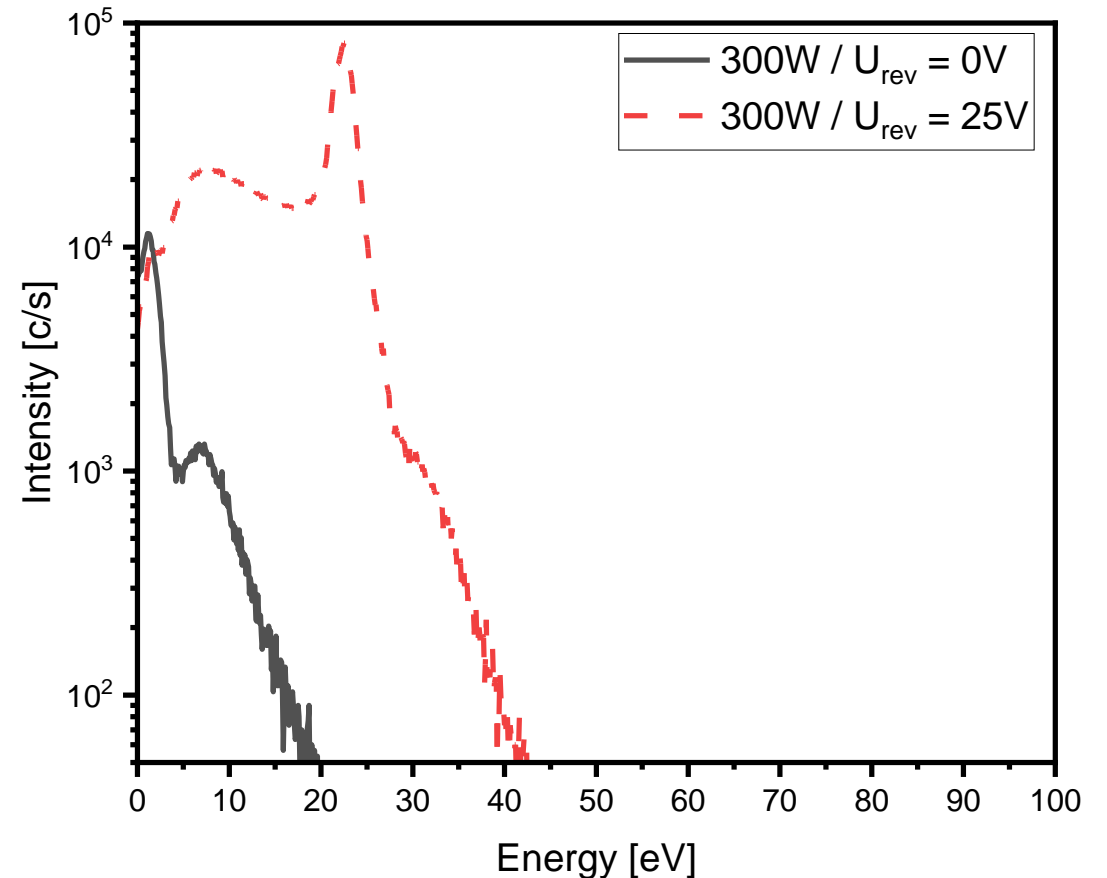
Coating activities – Modified 1.3 GHz cavity

- Energy analysis of Nb⁺ positive ions
 - A first peak is observed (~ 5 eV), which decrease gradually in intensity as U_{pos} increases. The ion population is influenced by U_{pos} but not enough to be significantly accelerated by it
 - With $U_{\text{pos}}=25\text{V}$, a new peak appears at an energy slightly above eU_{pos} . Similar tail is observed as the HiPIMS case only but up-shifted in energy by eU_{pos}



Coating activities – Modified 1.3 GHz cavity

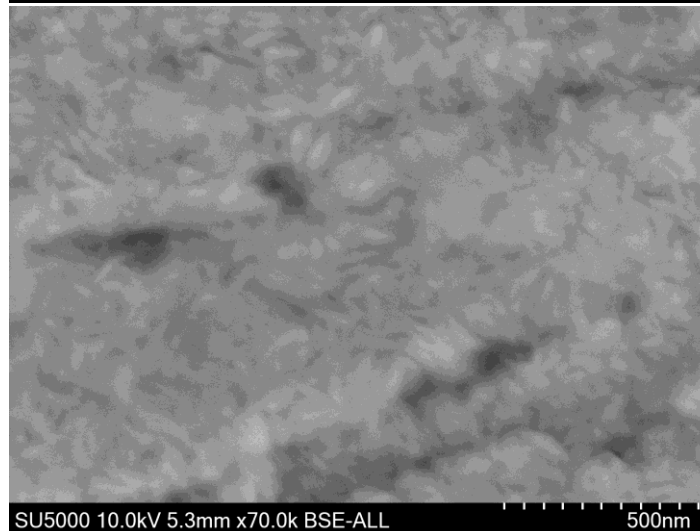
- Energy analysis of Kr^+ positive ions
 - Similar to Nb^+ - Up-shift to the right with an increase of intensity, slightly above eU_{pos} and followed by a drastic decrease. One assumption could be that the Kr^+ ions are accelerated but do not gain the full energy eU_{pos}



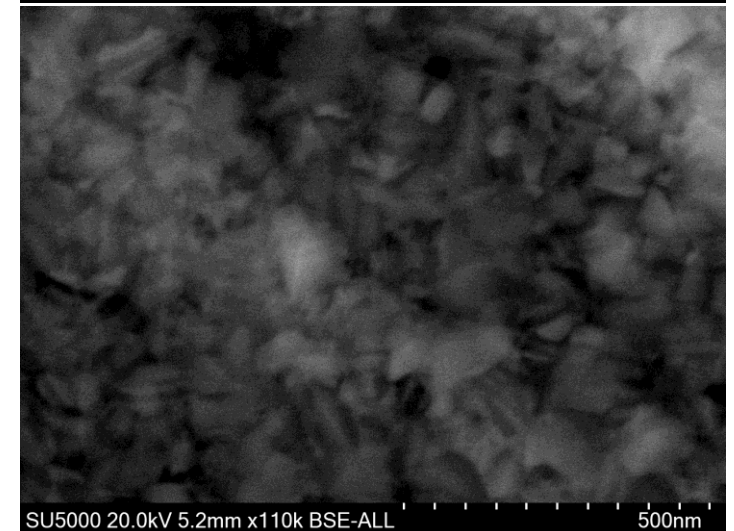
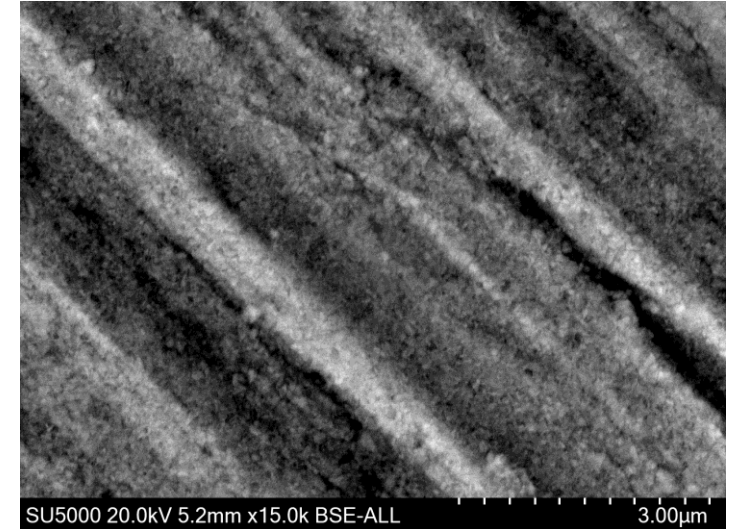
Coating activities – Modified 1.3 GHz cavity (reminder)

- Influence of bipolar HiPIMS on the film structure
 - Bipolar HiPIMS produces a denser film
 - Similar T_c ($\sim 9.2\text{K}$)

HiPIMS – 100W



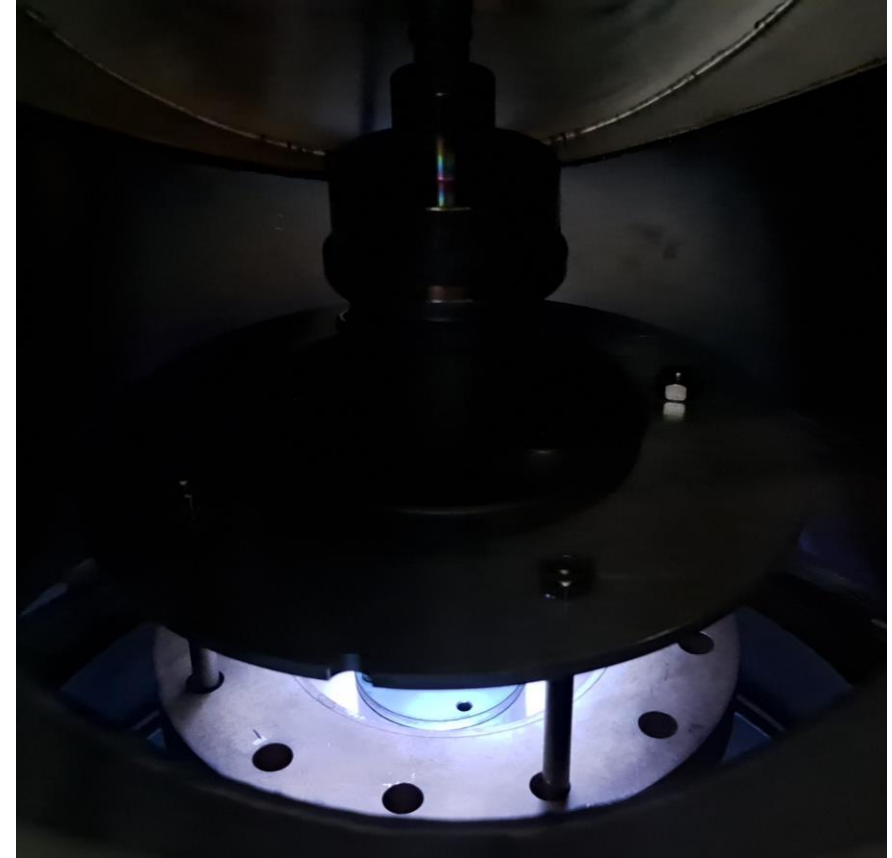
Bipolar HiPIMS – 100W



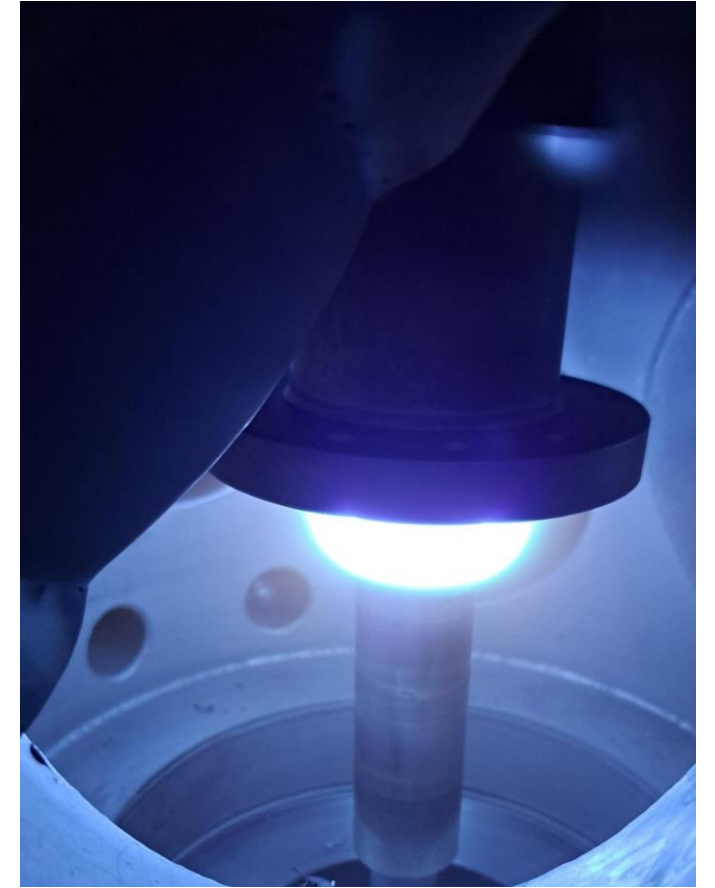
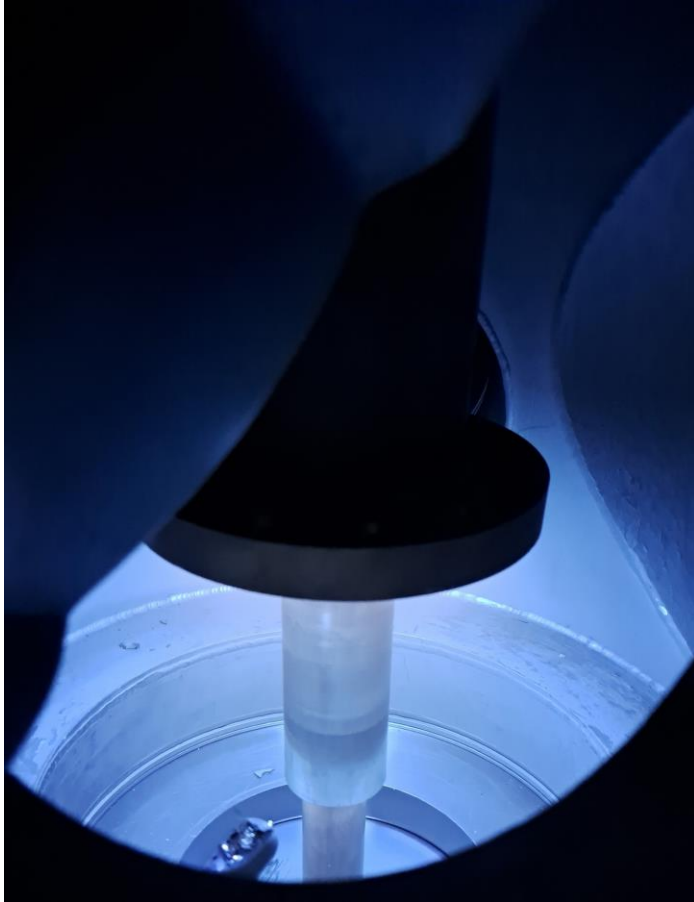
Coating activities - 1.3 GHz cavity

- DIVERS' Rig
 - Modification of the magnetron (between JEFF and DIVERS)
 - Chamber filled with 15 sccm of Kr, base pressure of 2×10^{-3} mbar
 - Deposition done for 6 hours in HiPIMS (480V / 830 mA / 400W / 9A / 1000Hz / 100us)

➔ Technical issues: the cavity was not getting coated at the bottom

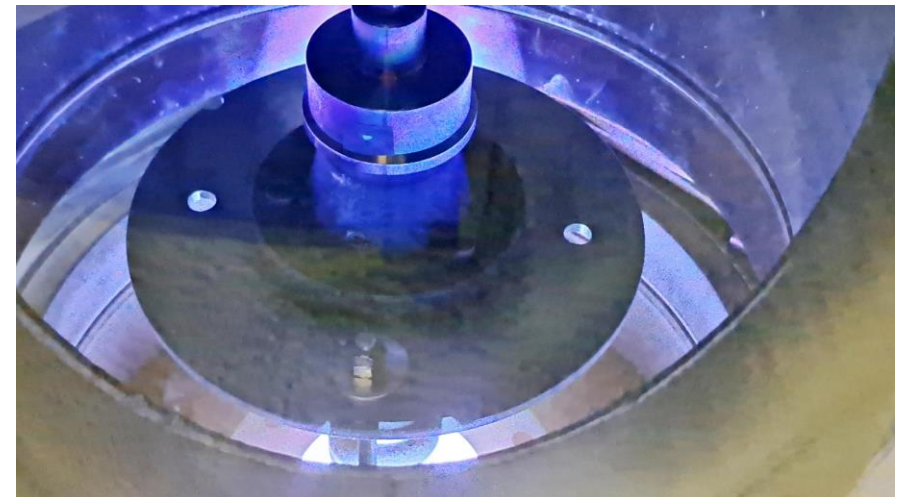
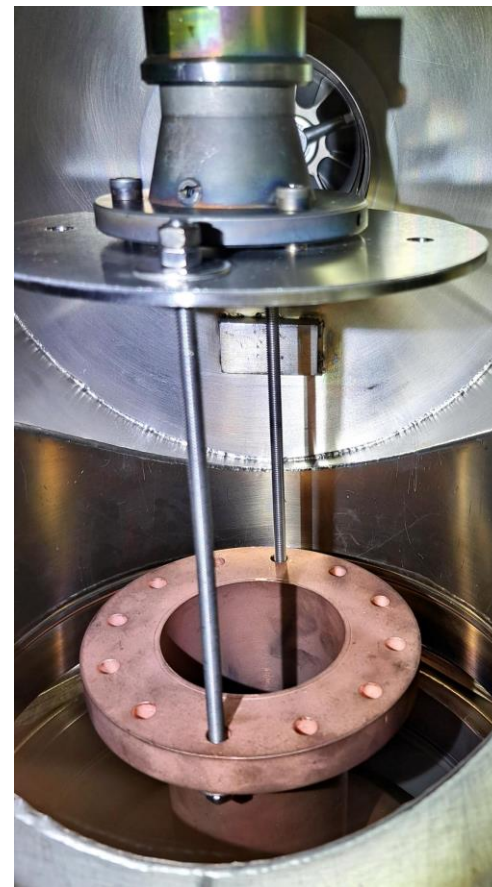


Coating activities - 1.3 GHz cavity

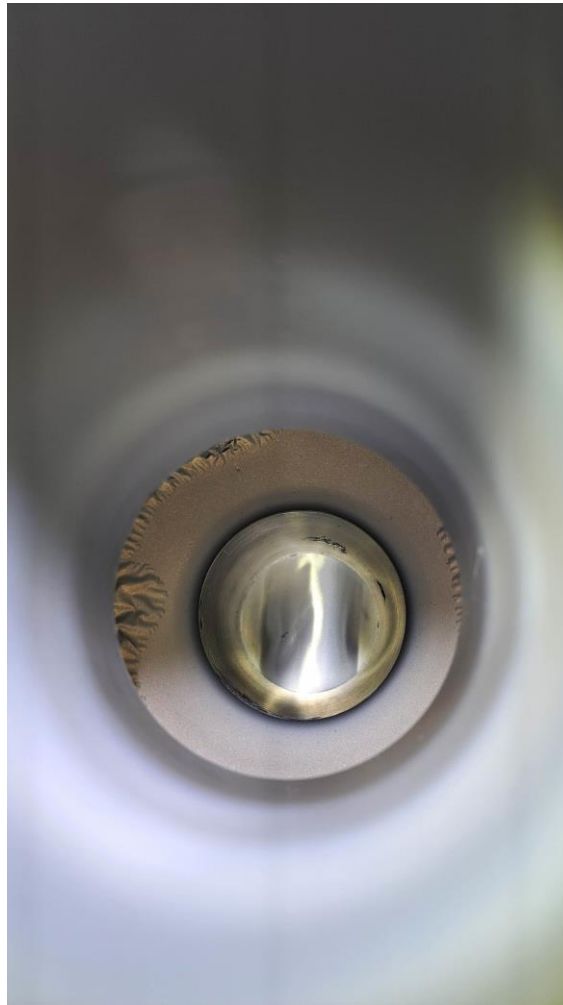


Coating activities - 1.3 GHz cavity

- DIVERS' Rig
 - Upgrade of the holder (top part), allows the cavity to go further down during deposition
 - New deposition for 4 hours
 - 15 sccm Kr, 2×10^{-3} mbar
 - 480V / 830 mA / 400W / 9A / 1000Hz / 100us



Coating activities - 1.3 GHz cavity

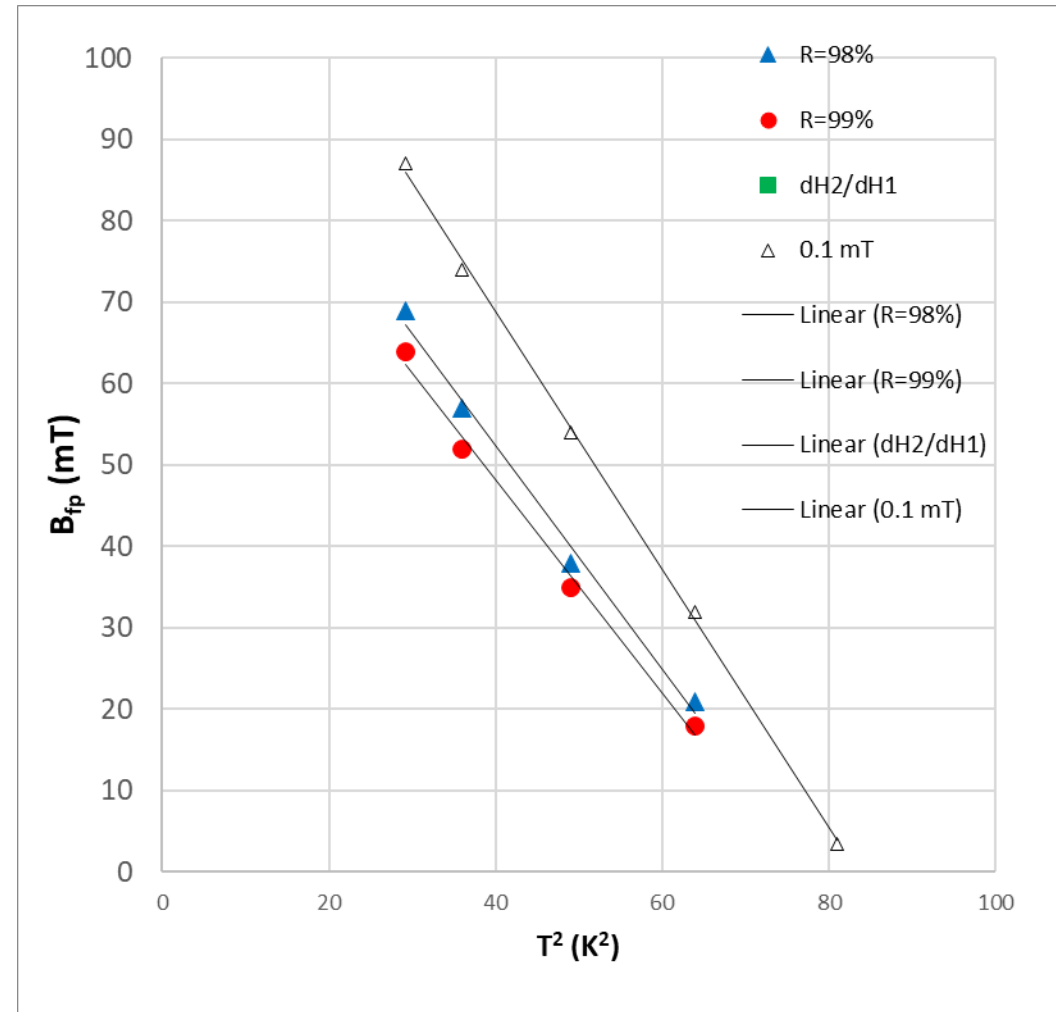
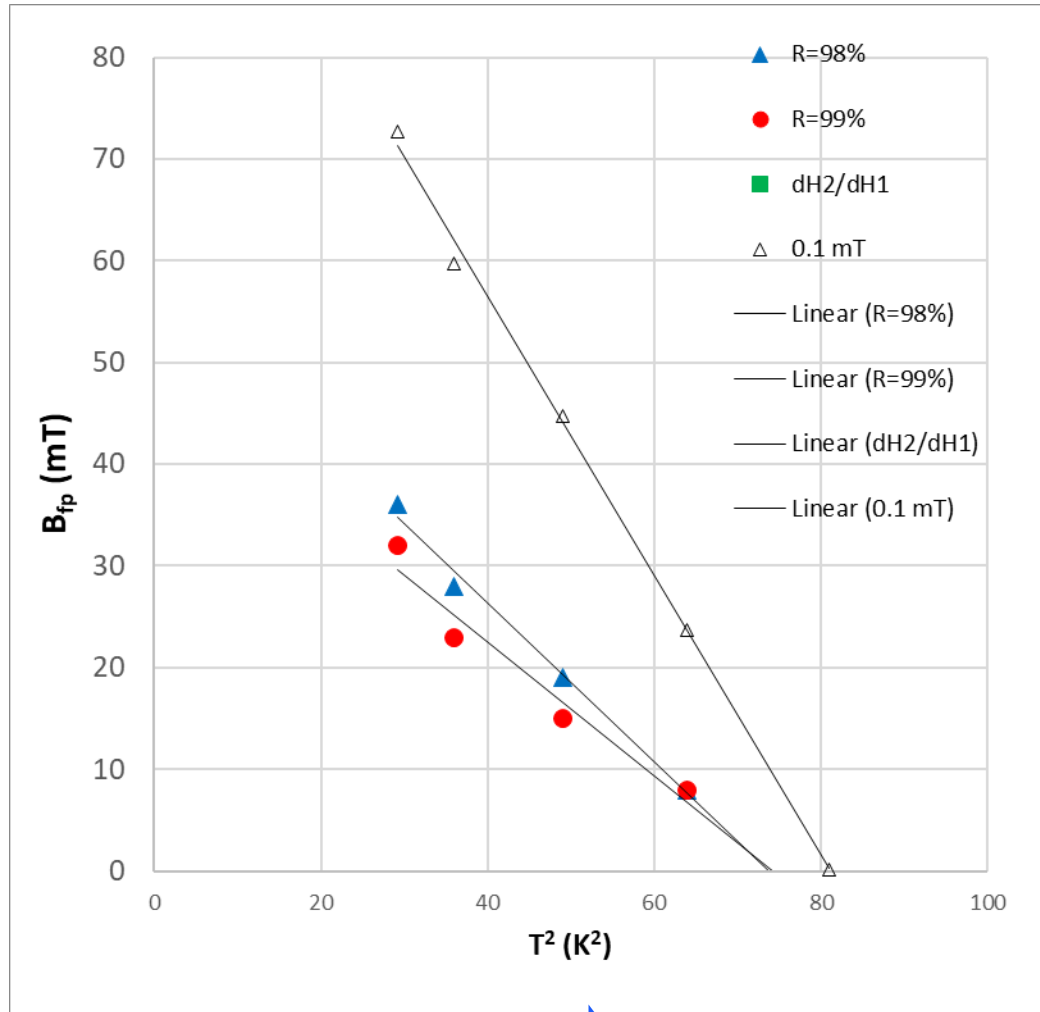


Coating activities – Disk samples in JEFF

- Study for IPAC'24
 - Samples coated using HiPIMS at 300W for 4 hours at a pressure of 6×10^{-3} mbar
 - Parameters: 370V / 805mA / 300W / 11A / 1000Hz / 100us



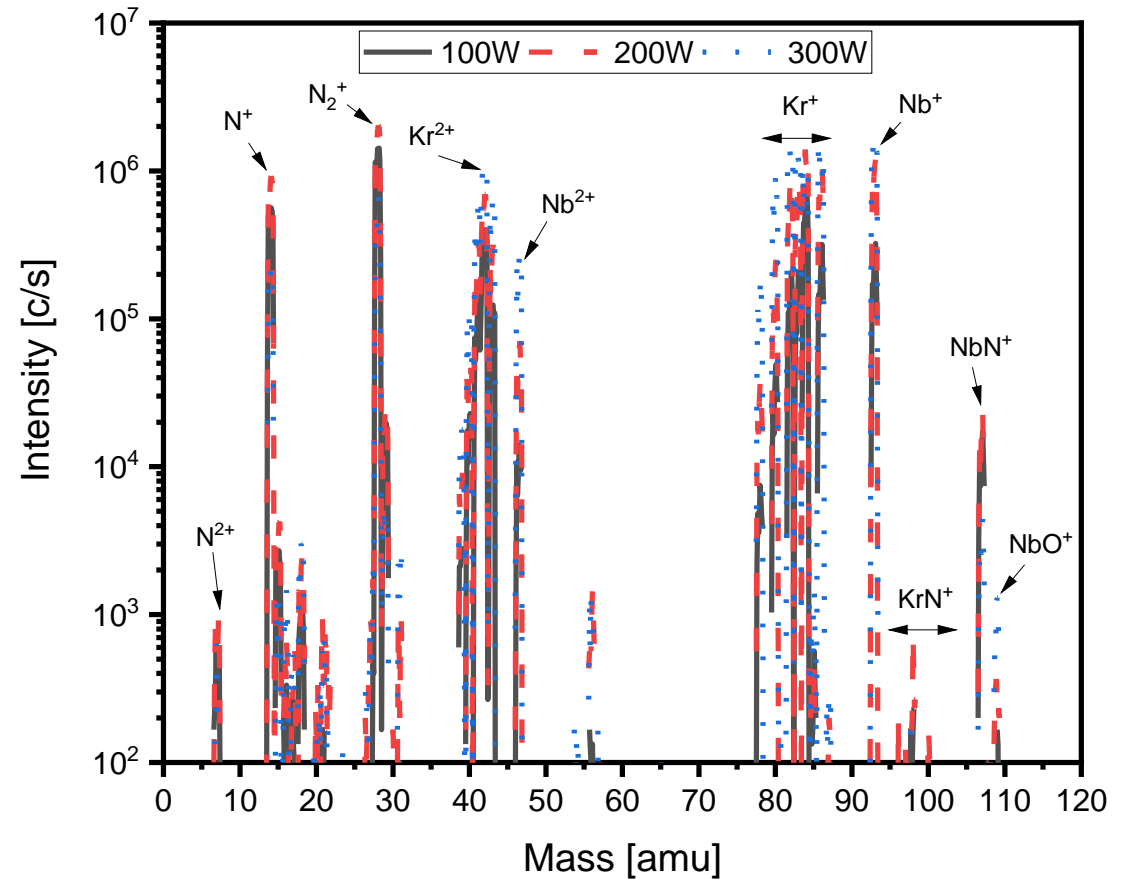
Coating activities – Disk samples in JEFF



Investigation of NbN: influence of HiPIMS power

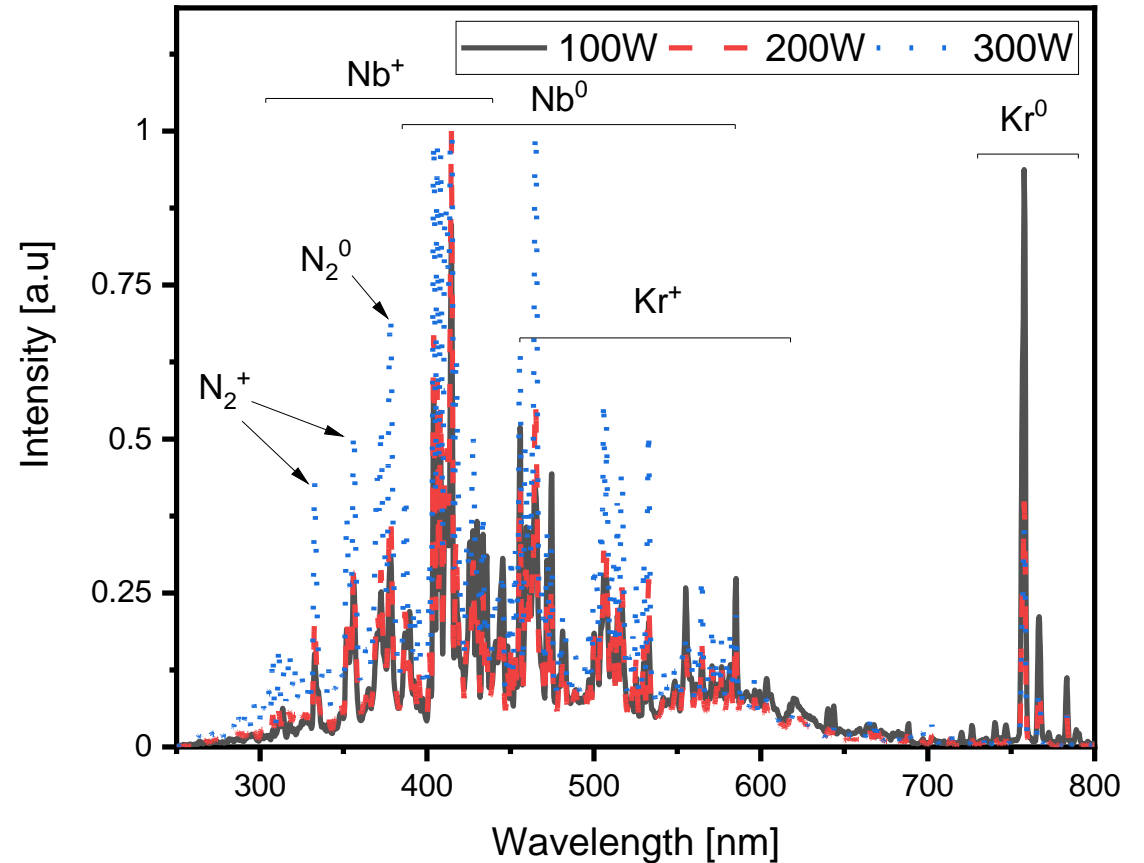
- Mass analysis and energy analysis in HiPIMS
 - Chamber filled with a 20 sccm flow rate of Kr and 2 sccm of N₂. Base pressure of 3.7x10⁻³ mbar
 - HiPIMS parameters:
neg PW 100us / Freq 1000Hz
100W: 721V / 139mA / 12A
200W: 730V / 275mA / 12A
300W: 567V / 530mA / 11A

➔ High reactivity with multiple recombinations

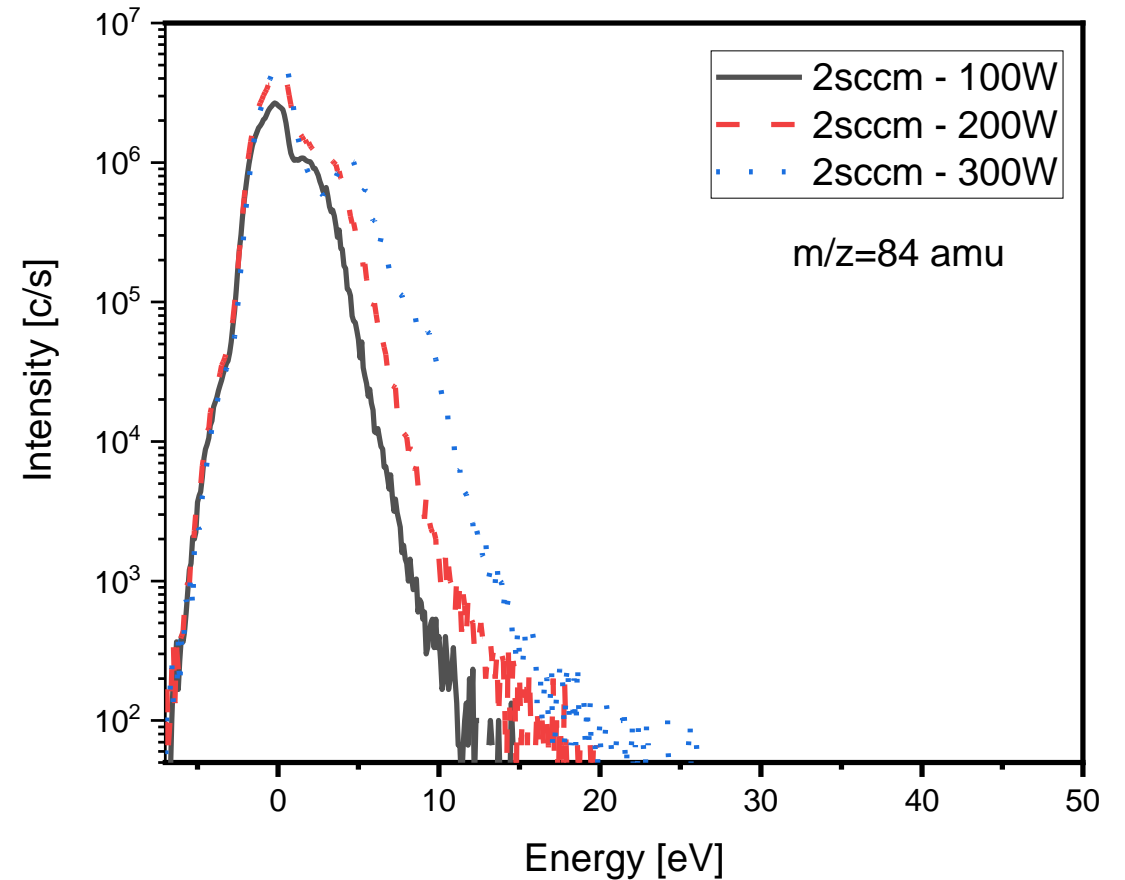
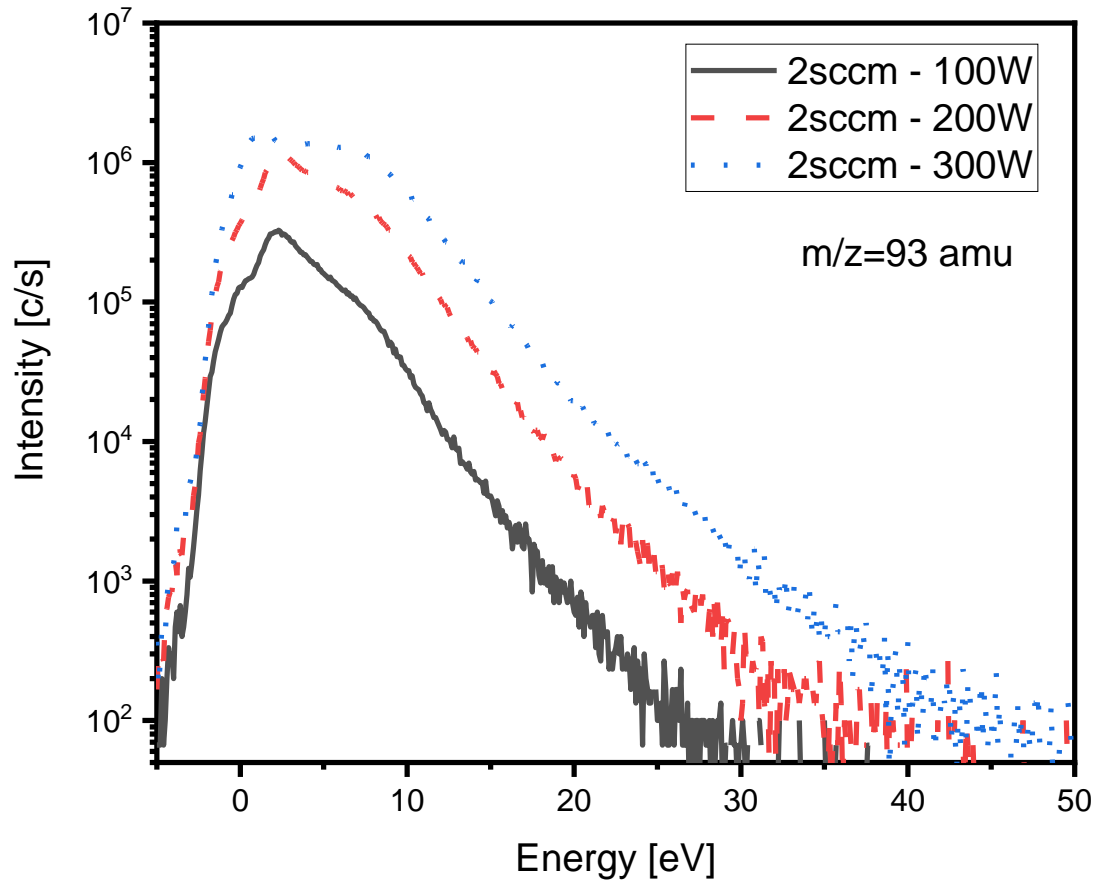


Investigation of NbN: OES for different power conditions

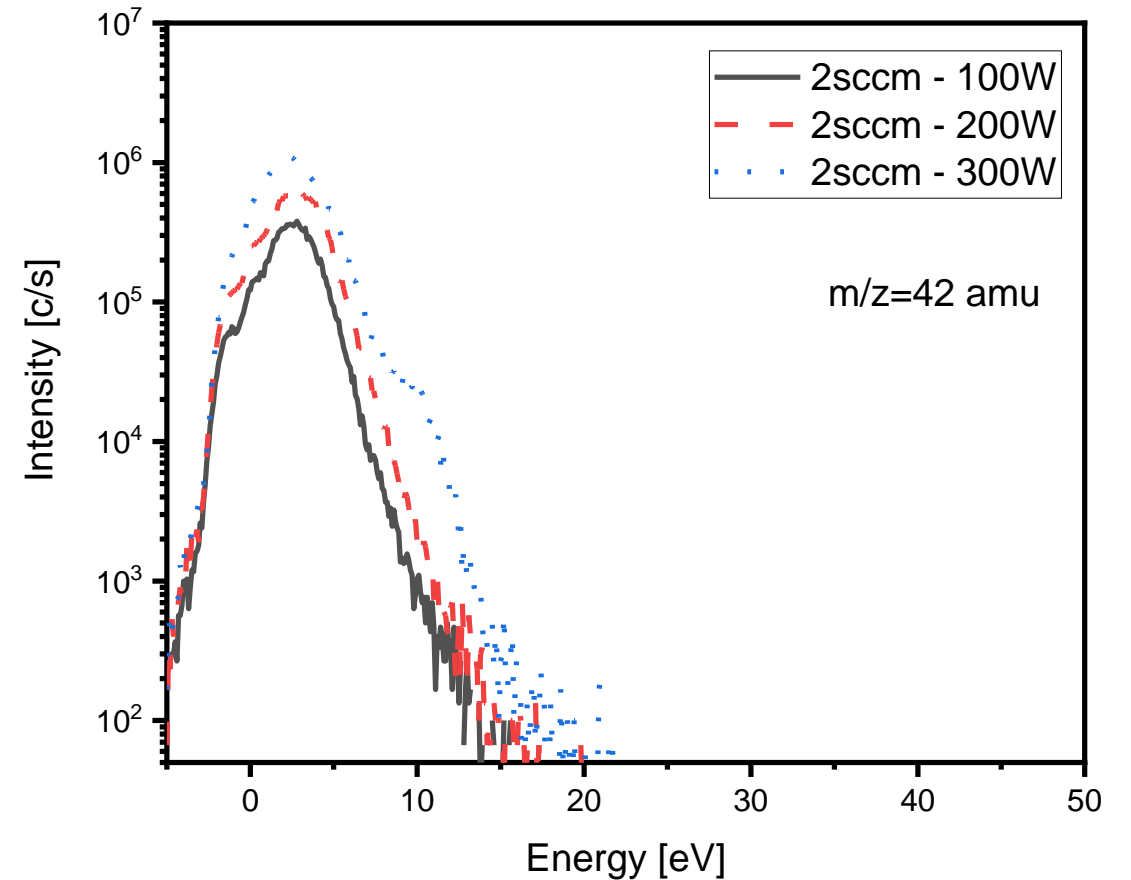
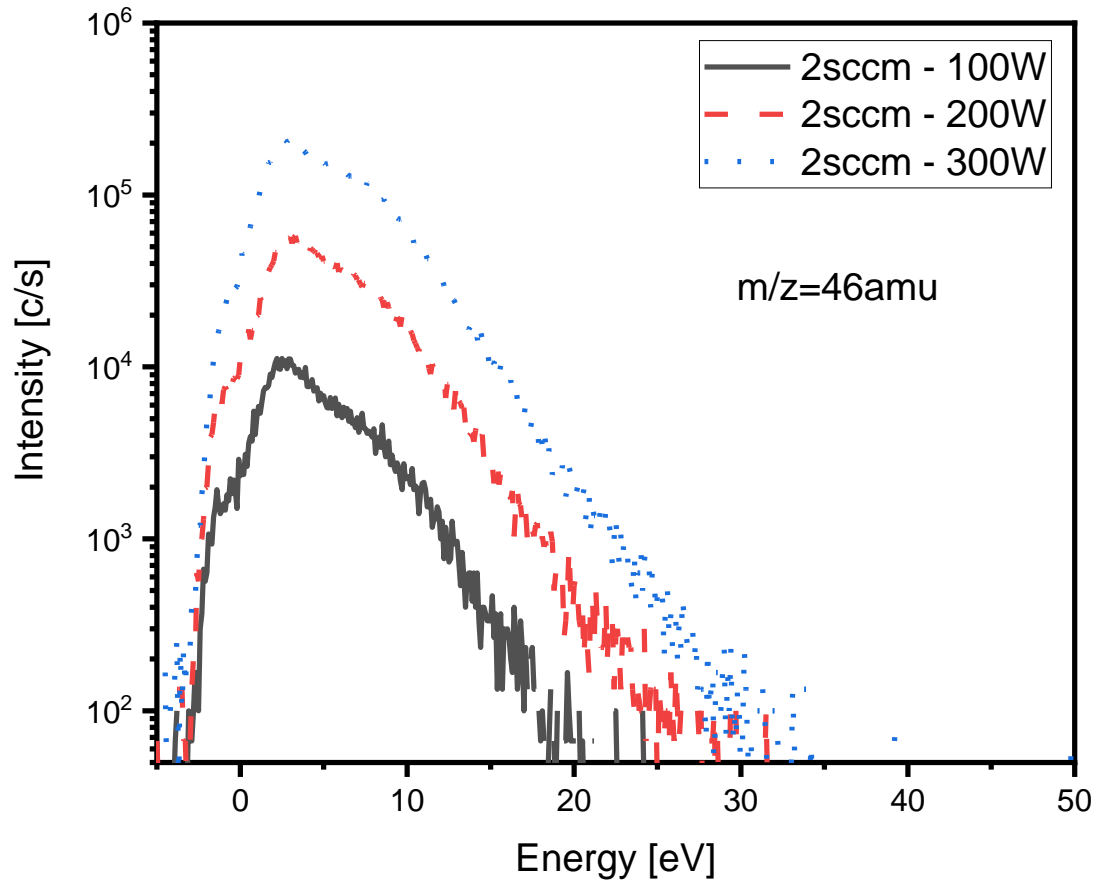
- Overlap of Nb^+ , Nb^0 , Kr^+ , N_2^+ and N_2^0 lines
- Increase of power lead to an increase of line intensity which benefits mainly Nb^+ , Nb^0 , Kr^+ , N_2^+ and N_2^0



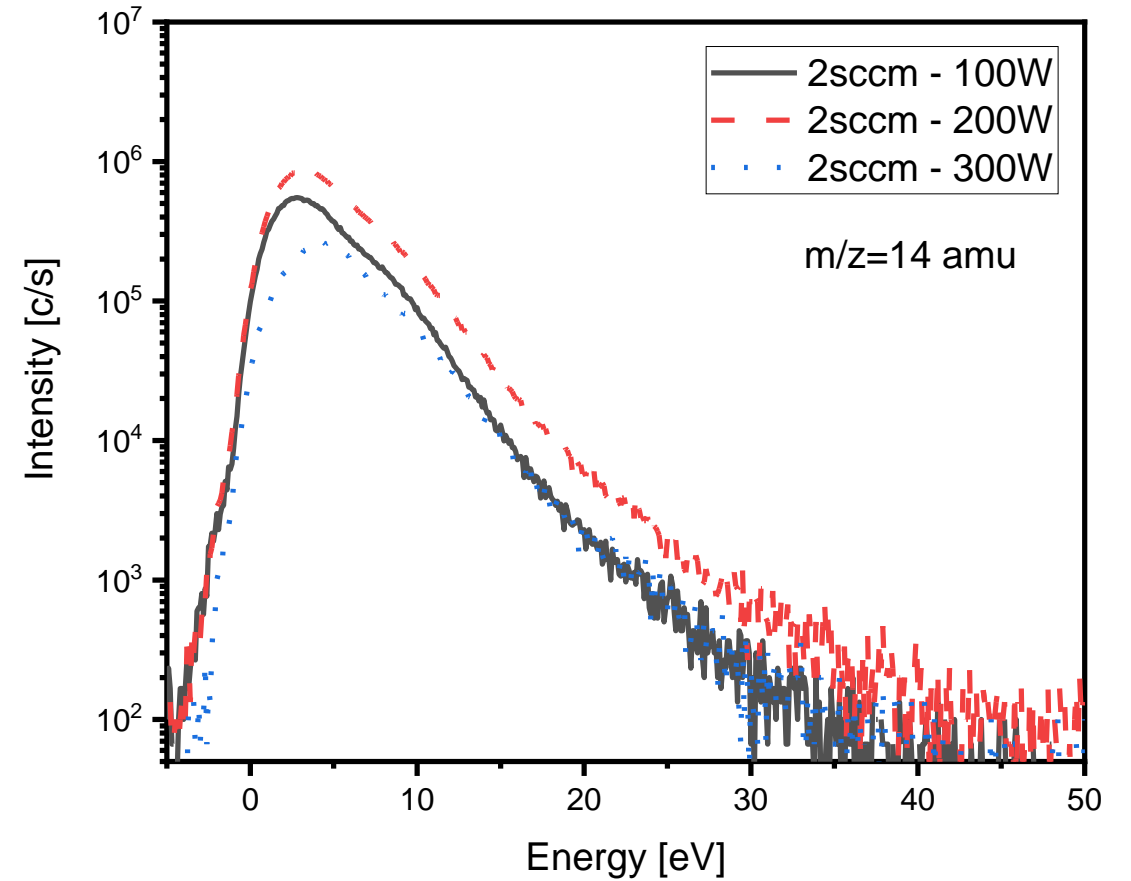
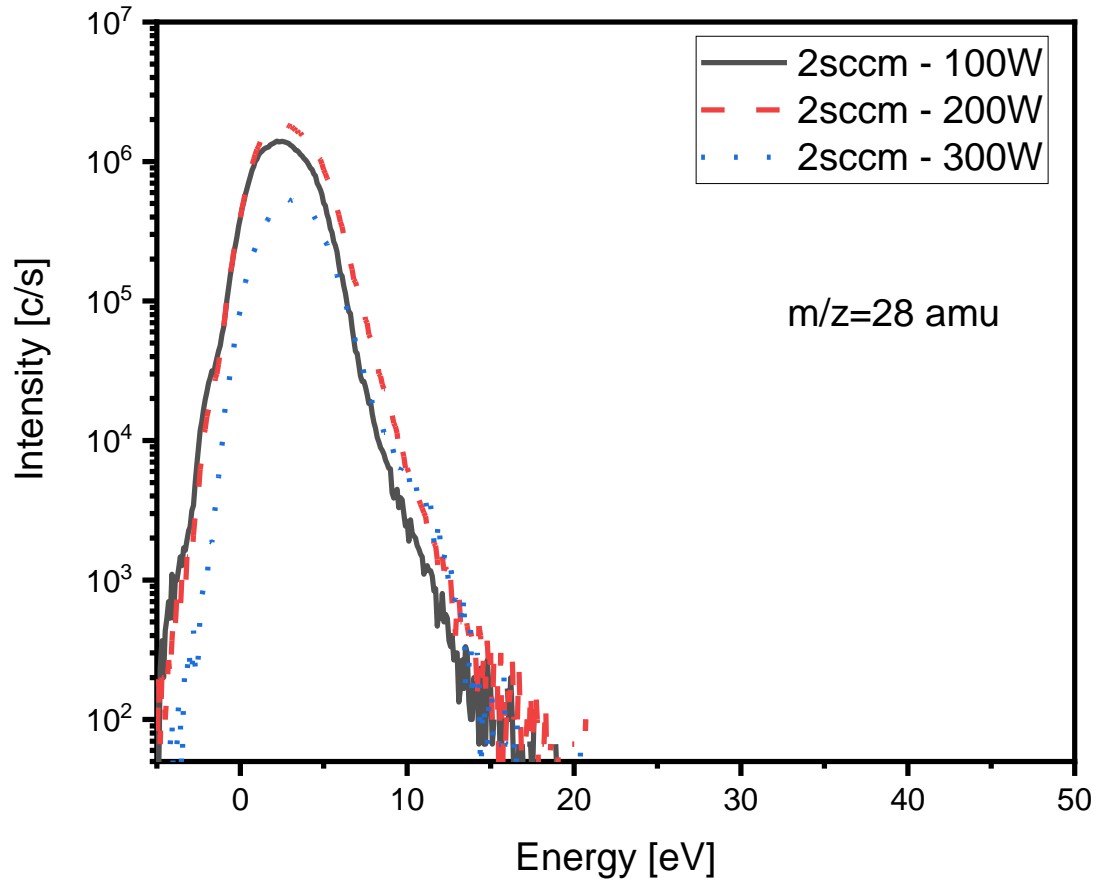
Investigation of NbN: IEDF of Nb⁺ and Kr⁺



Investigation of NbN: IEDF of Nb²⁺ and Kr²⁺

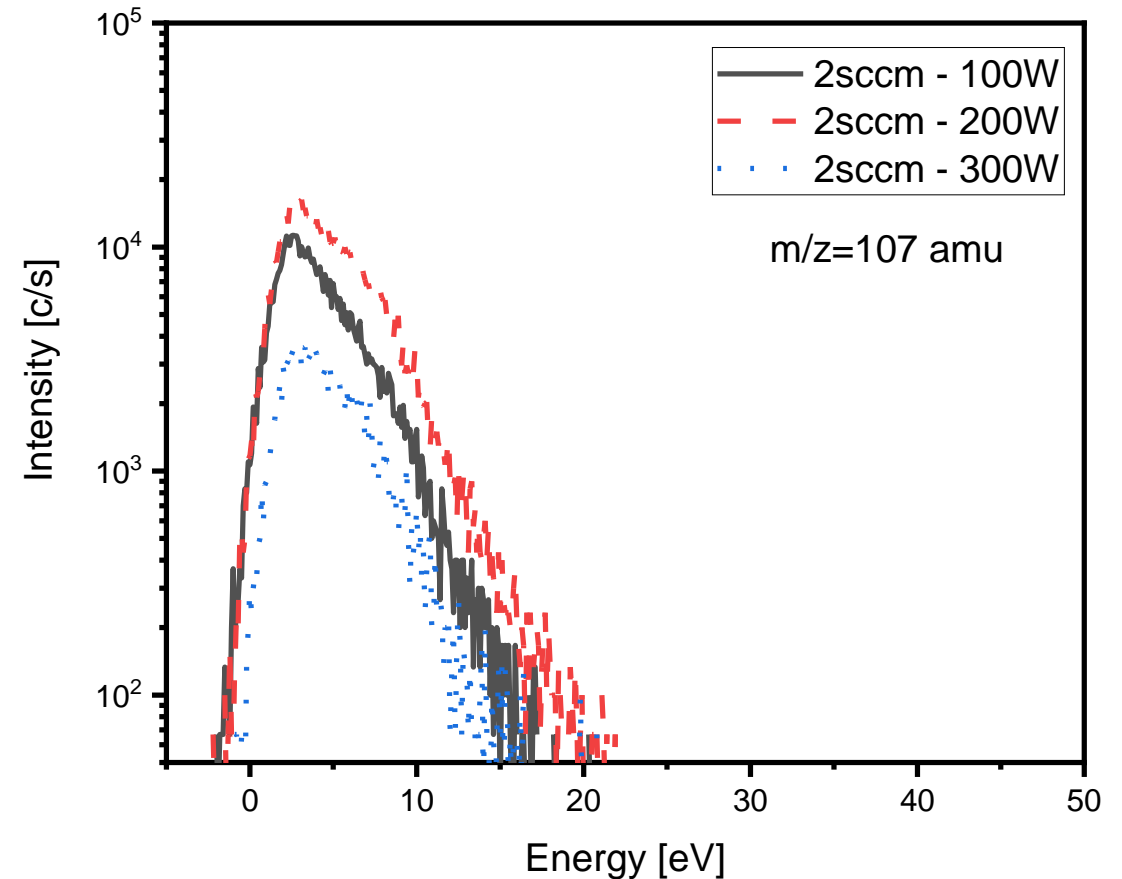


Investigation of NbN: IEDF N_2^+ and N^+



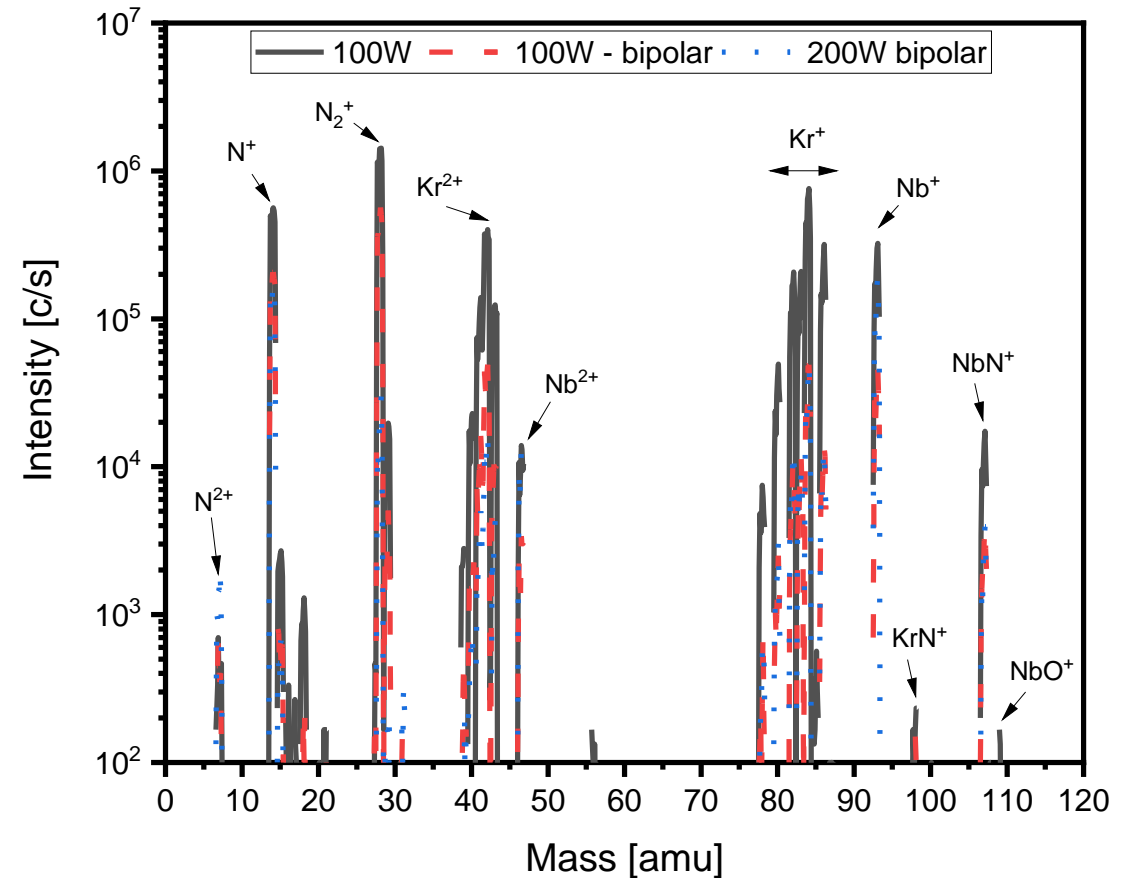
Investigation of NbN: evolution of NbN⁺

- 100W and 200W case are roughly similar. 300W seems to increase the intensity of NbO but not NbN.
- System not baked before measurements, oxygen comes mainly from residual water present in the chamber.
- Mass at 56 amu ?



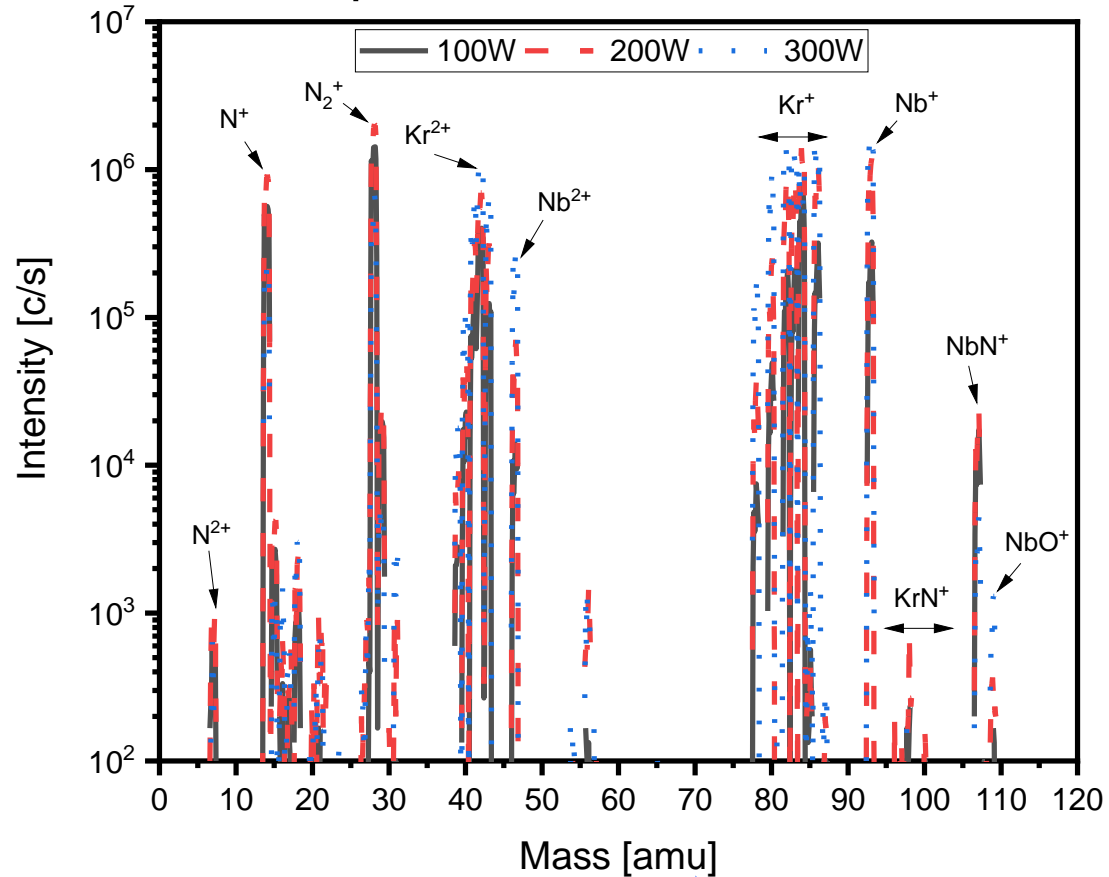
Investigation of NbN: comparison HiPIMS and bipolar HiPIMS

- Comparison between unipolar and bipolar HiPIMS
- For positive kick, pulse width of 200us and U_{pos} set to 25V
- 56 amu drastically reduced, likely to be a contaminant outgassing during the run

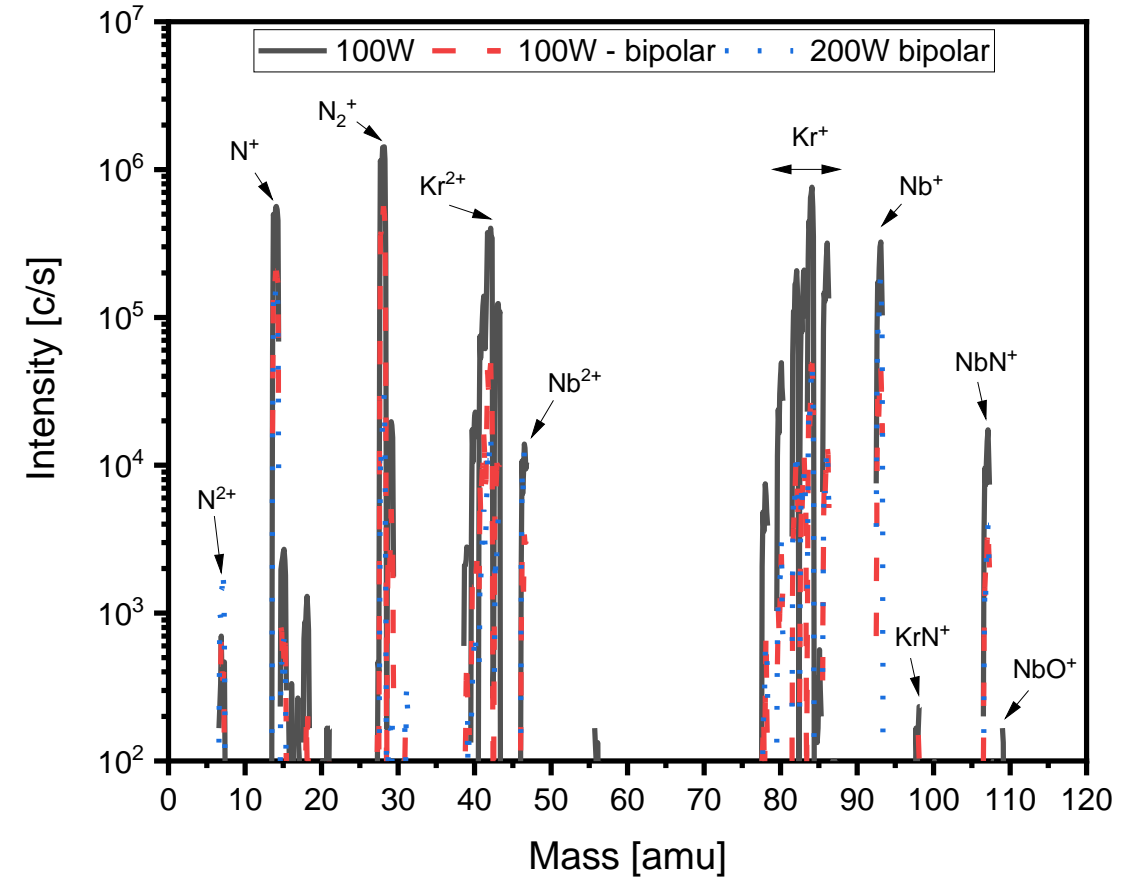


Investigation of NbN: power influence between HiPIMS and bipolar HiPIMS

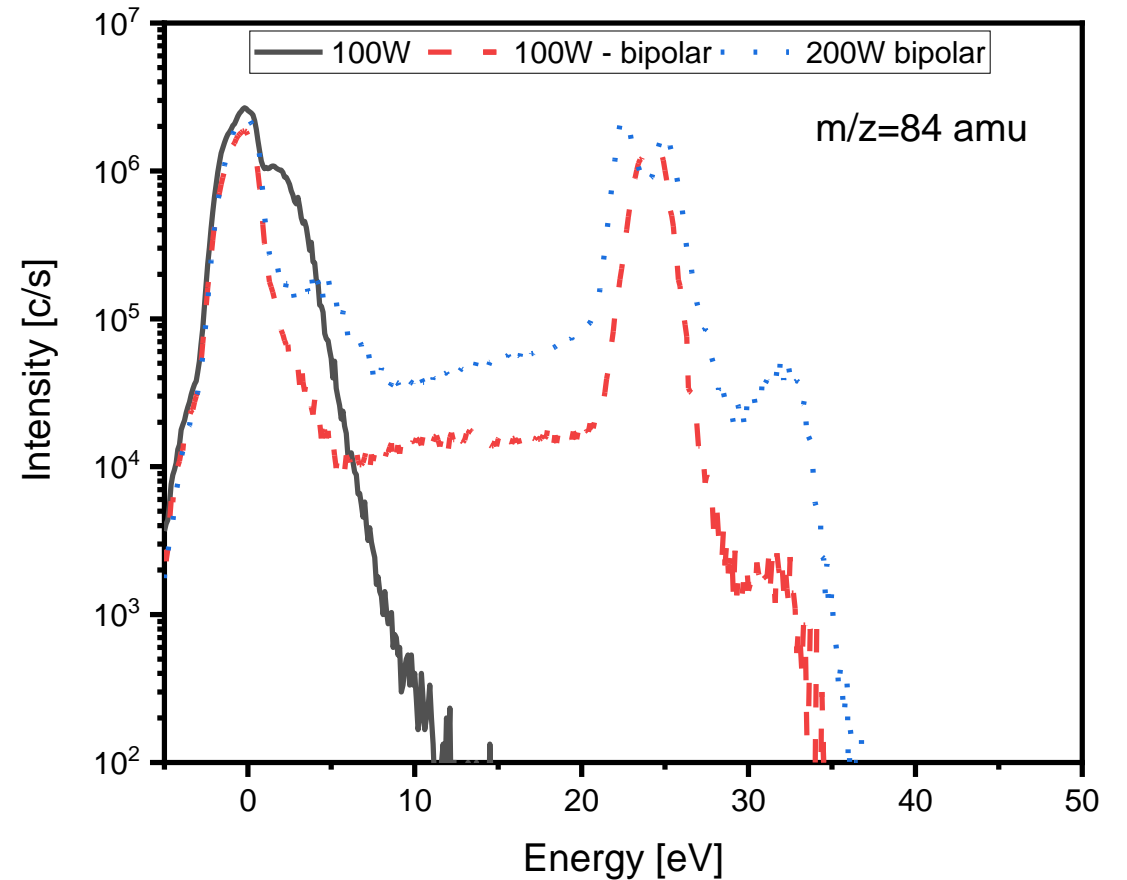
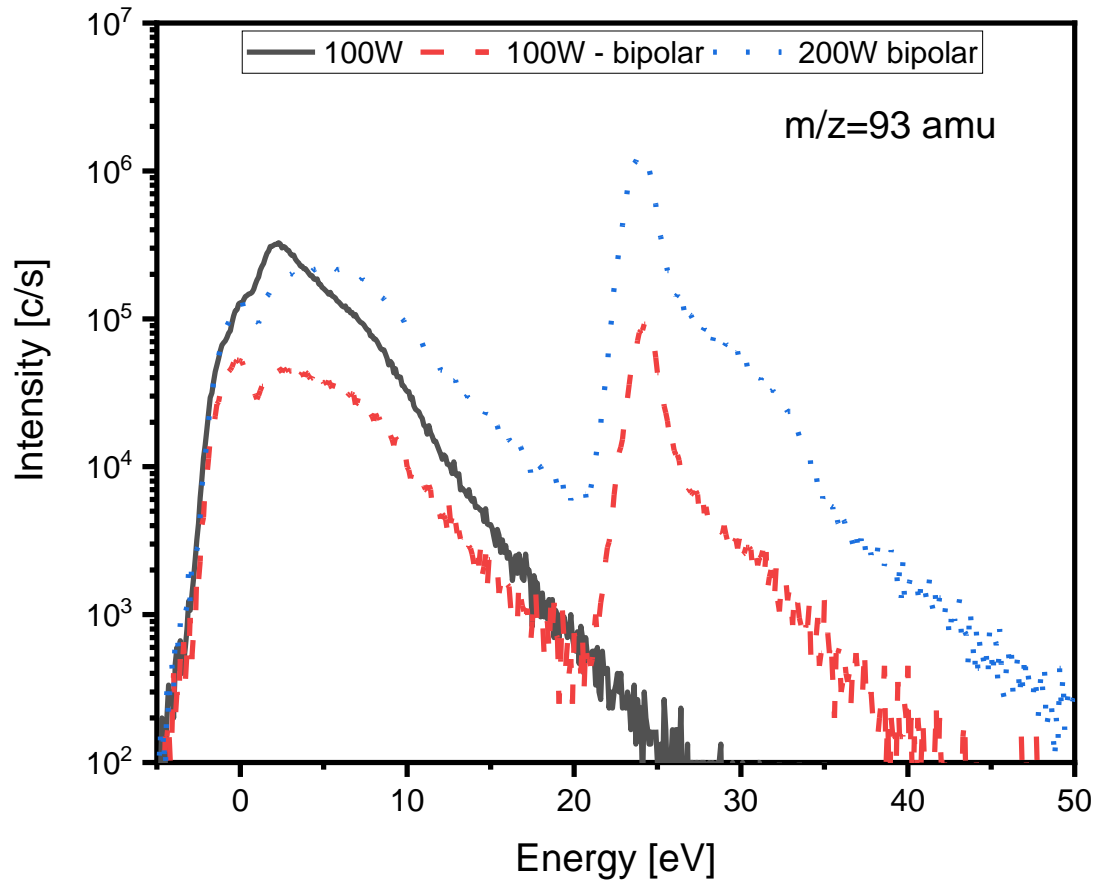
Unipolar – Power influence



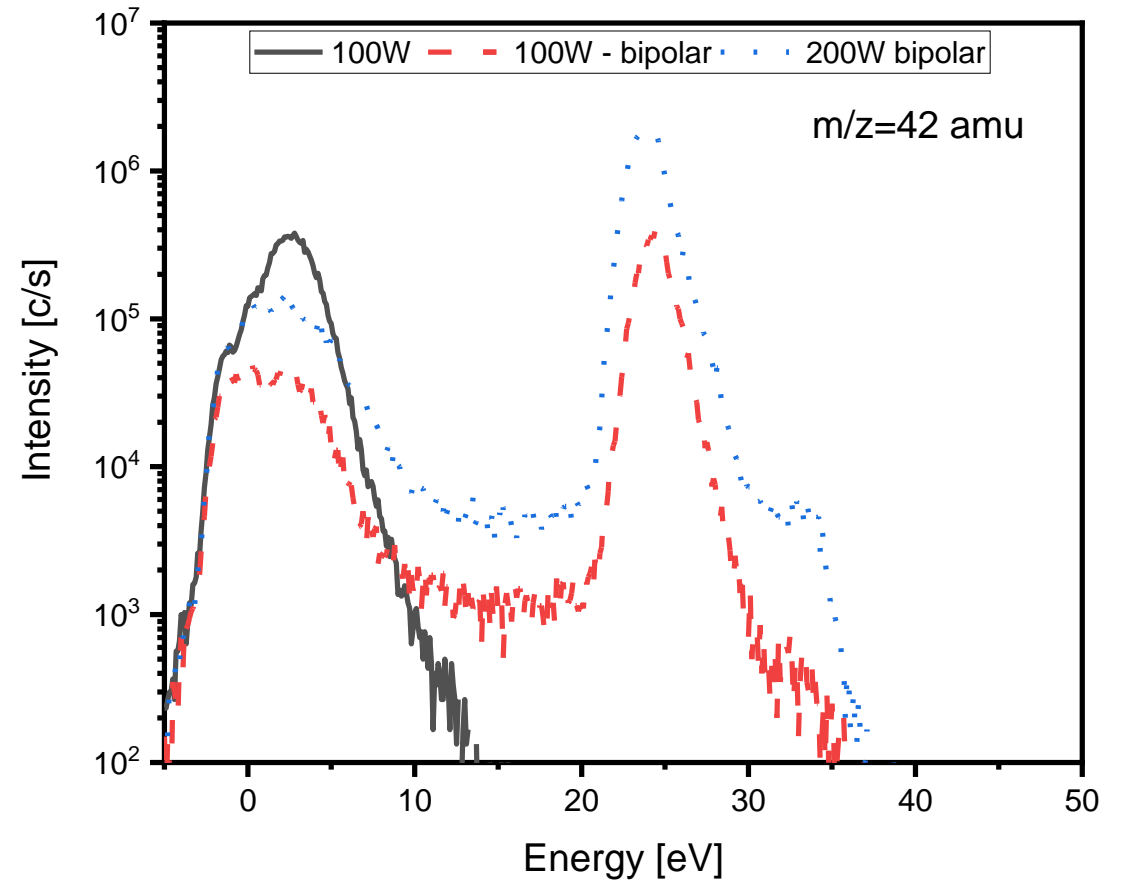
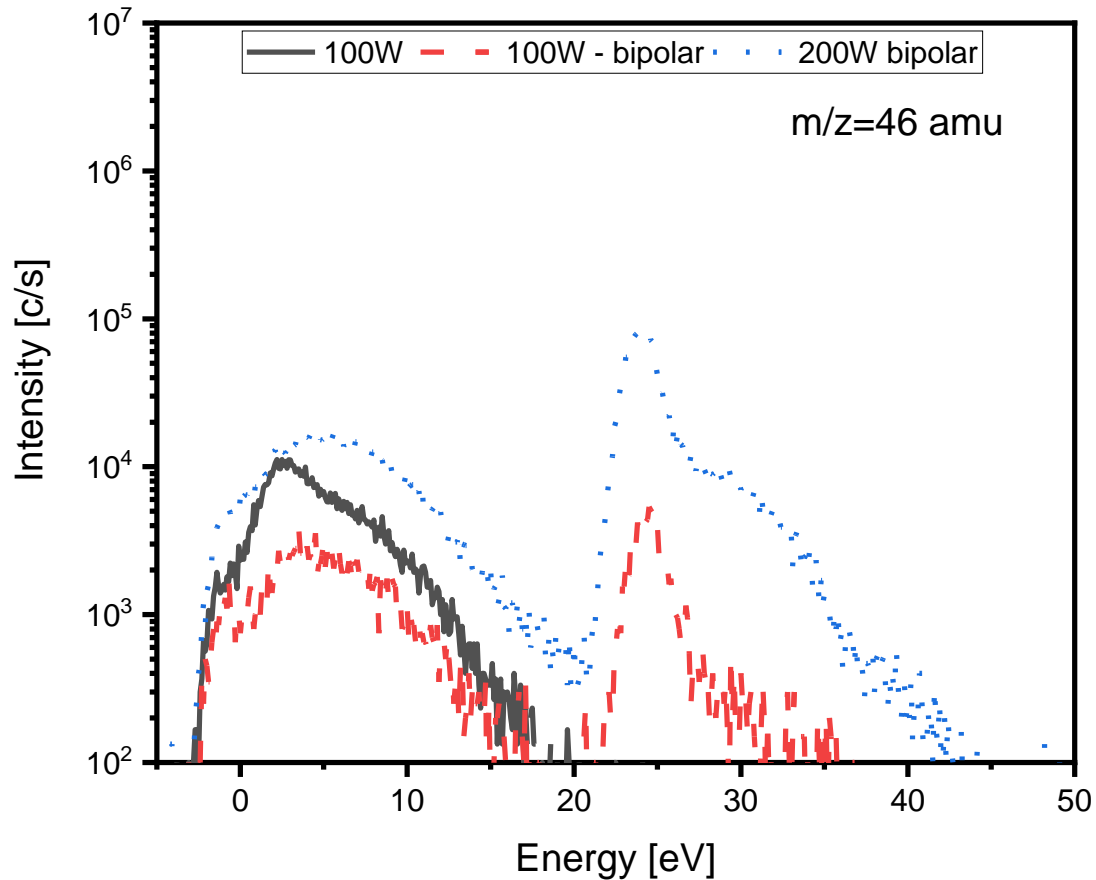
Bipolar – Power influence



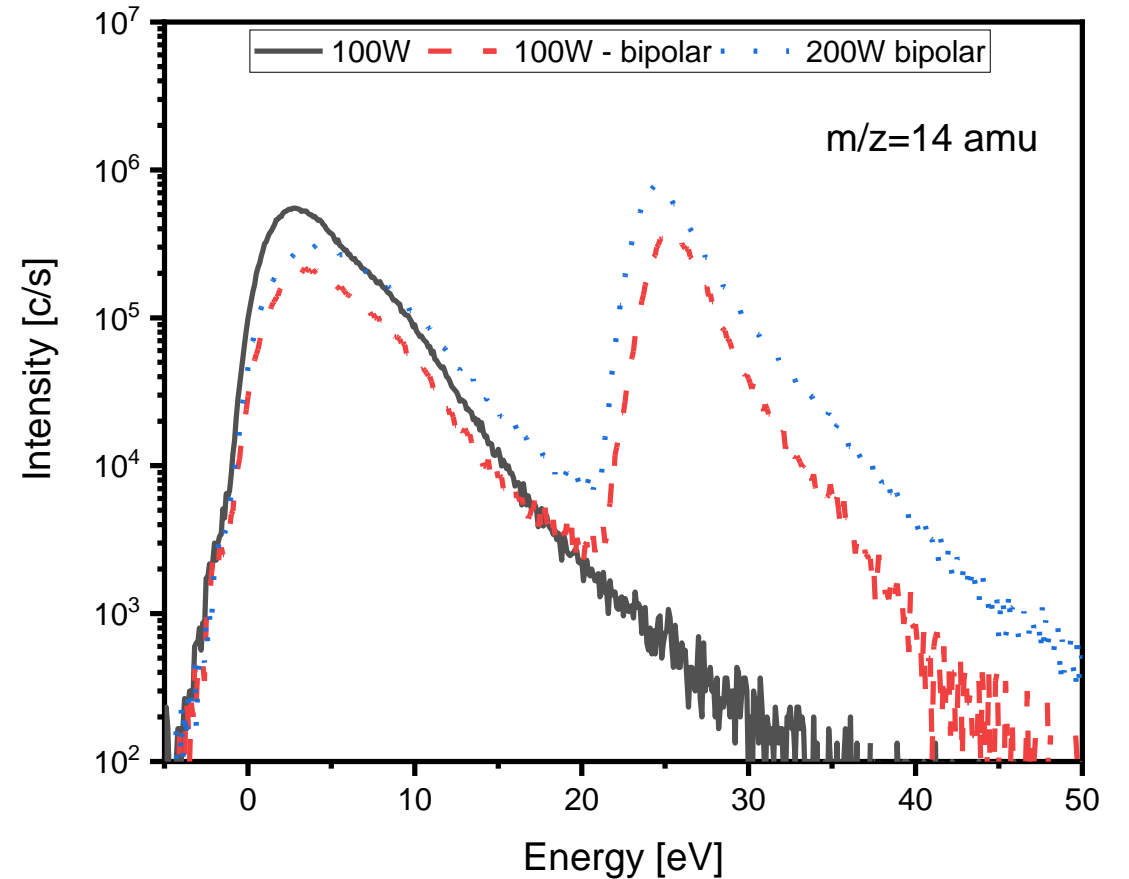
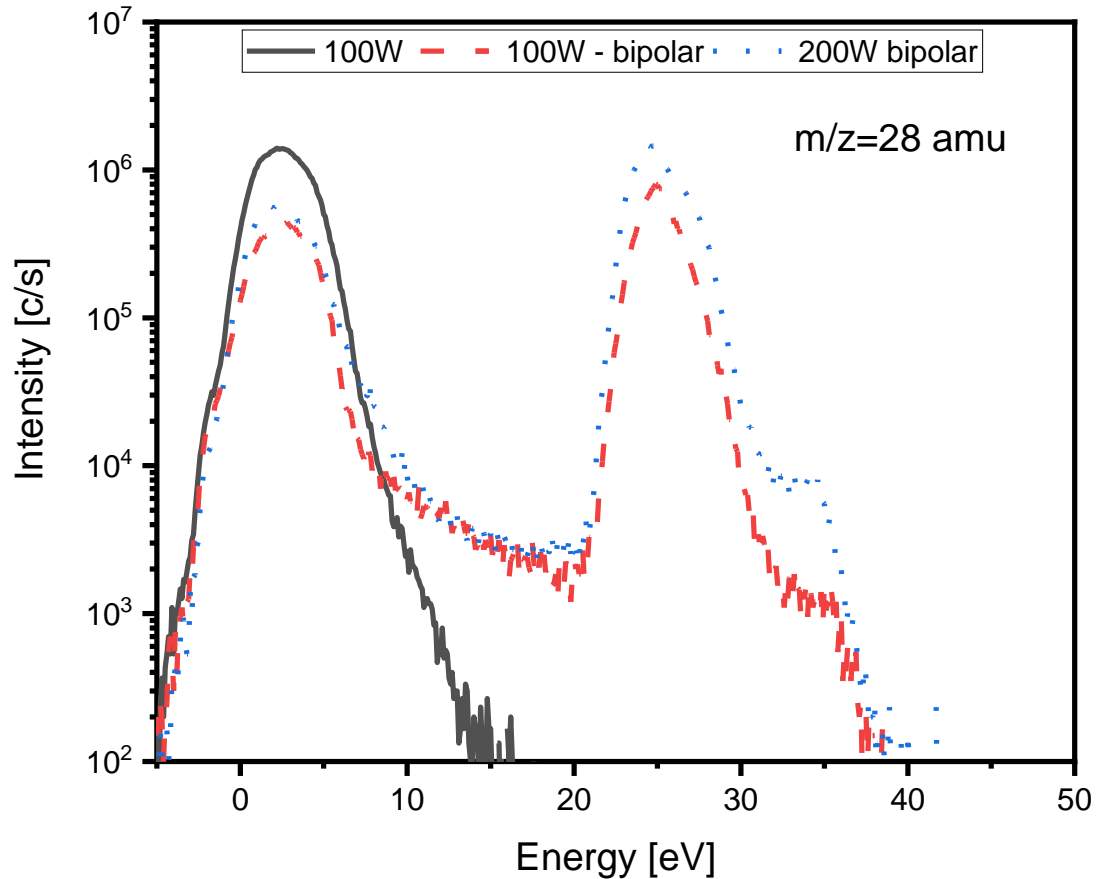
Investigation of NbN: IEDF of Nb⁺ and Kr⁺



Investigation of NbN: IEDF of Nb^{2+} and Kr^{2+}

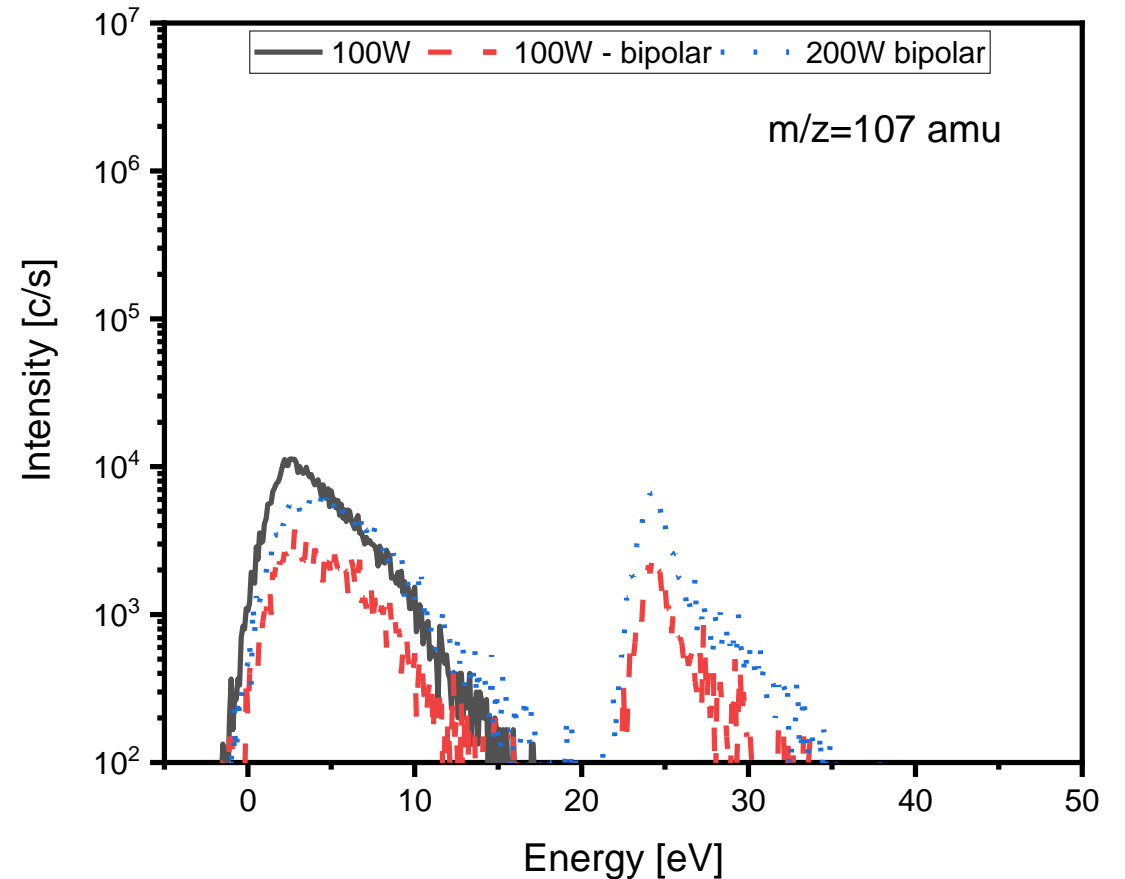


Investigation of NbN: IEDF of N_2^+ and N^+



Investigation of NbN: IEDF of NbN⁺

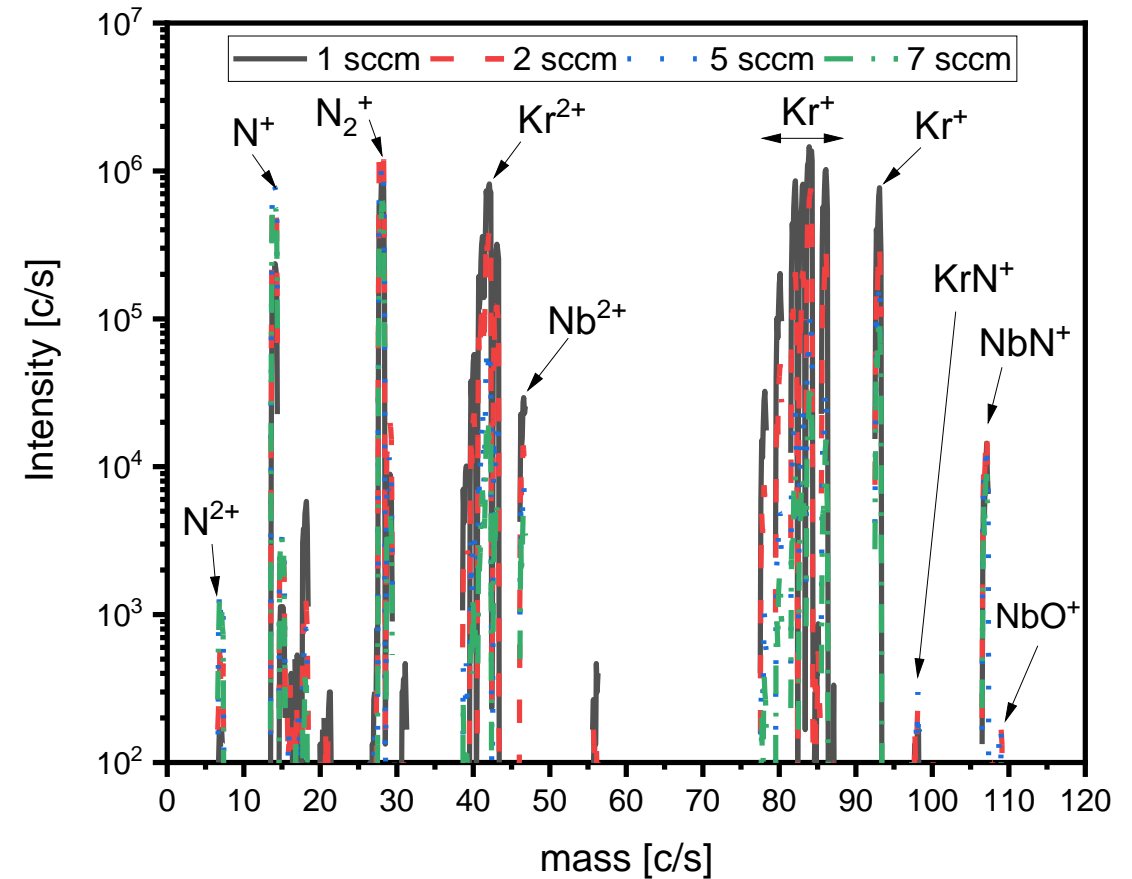
- As seen in previous results, initial peak intensity is reduced for the same in put power. Increasing the power balance the peak drop
- Shift according to eU_{pos}
- N₂ follows a similar trend as Kr



Investigation of NbN: flow rate influence in HiPIMS

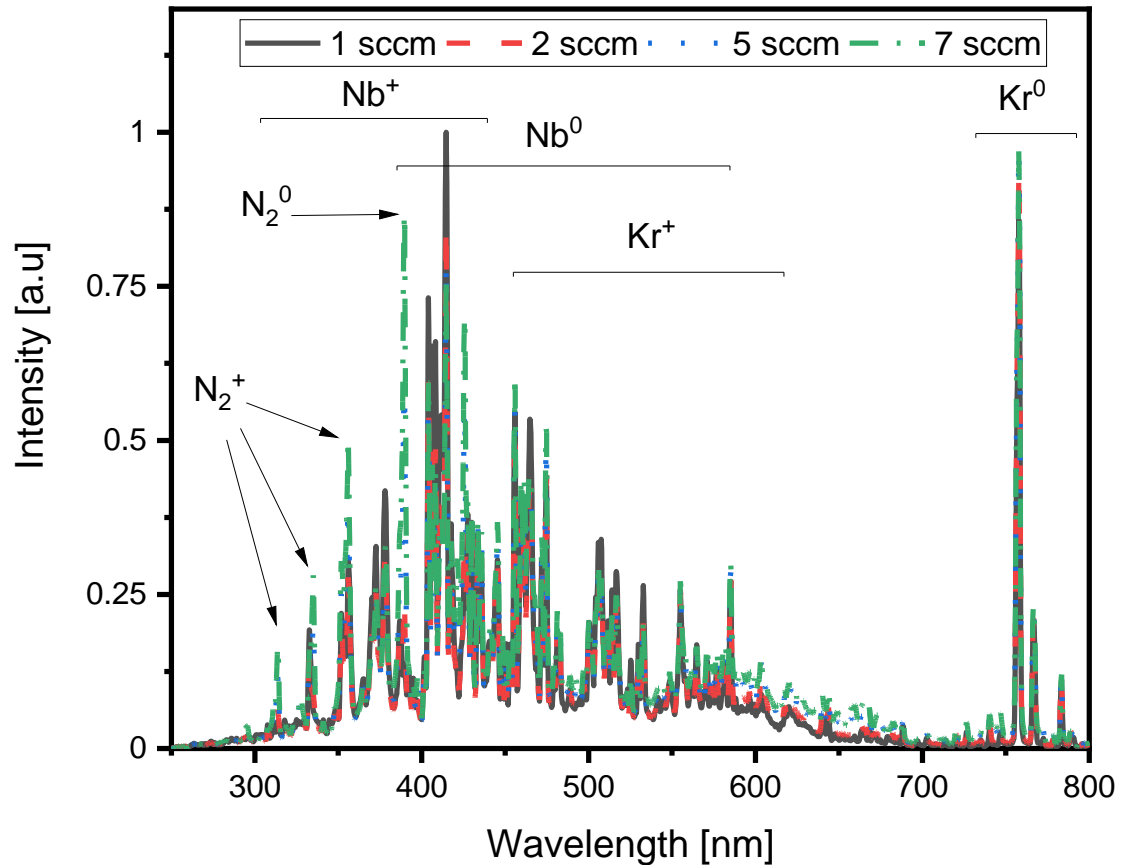
- Influence of N₂ flow rate
 - Flow rate: 1, 2, 5, 7 sccm
 - HiPIMS parameters (100us / 1000Hz)
 - 1 sccm: 595V / 168mA / 10A
 - 2 sccm: 721V / 139mA / 12A
 - 5 sccm: 766V / 127mA / 13A
 - 7 sccm: 806V / 124mA / 13A

Pressure stabilized at 4×10^{-3} mbar

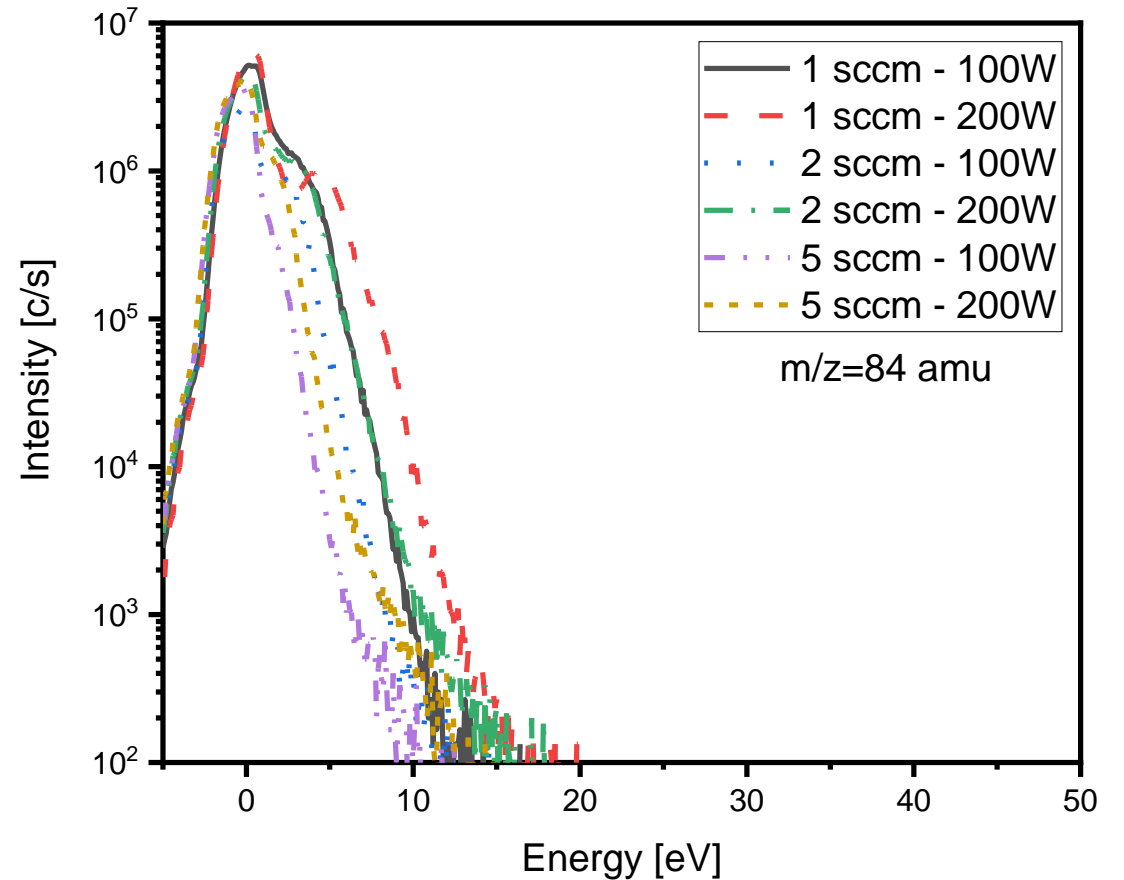
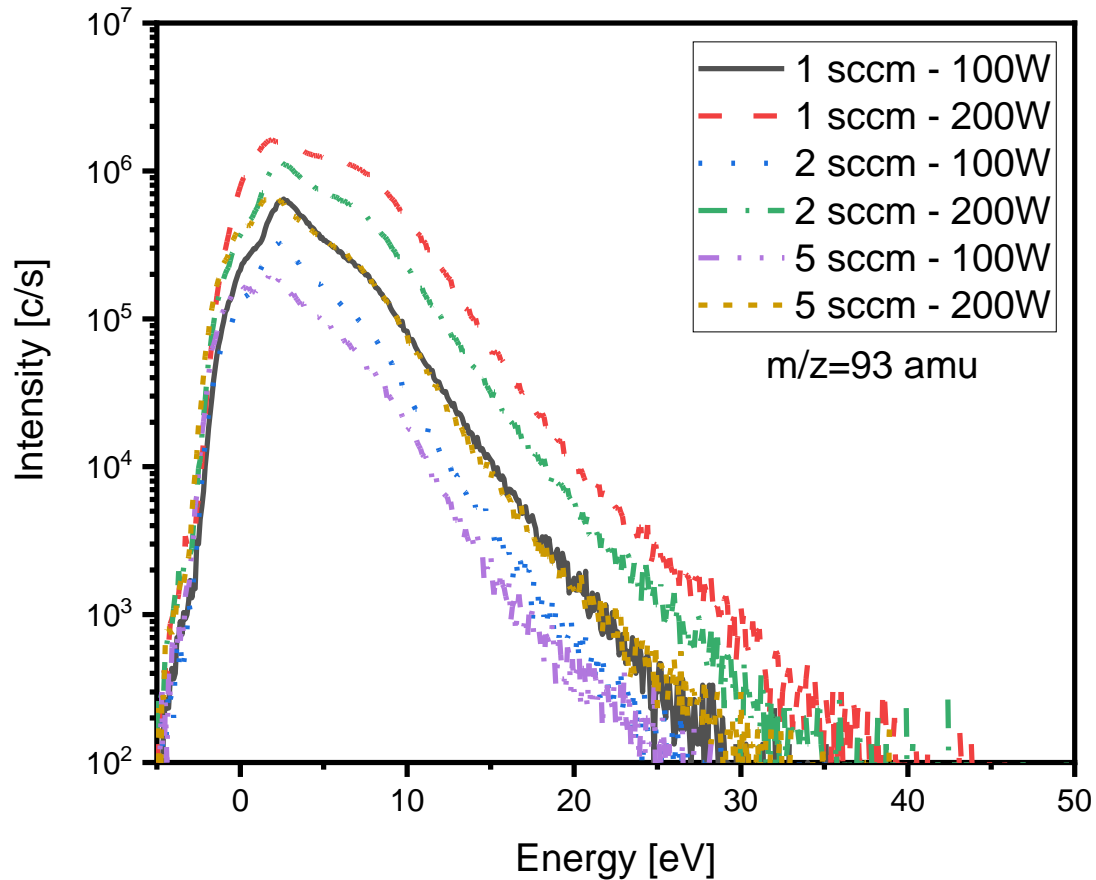


Investigation of NbN: OES at different flow rate

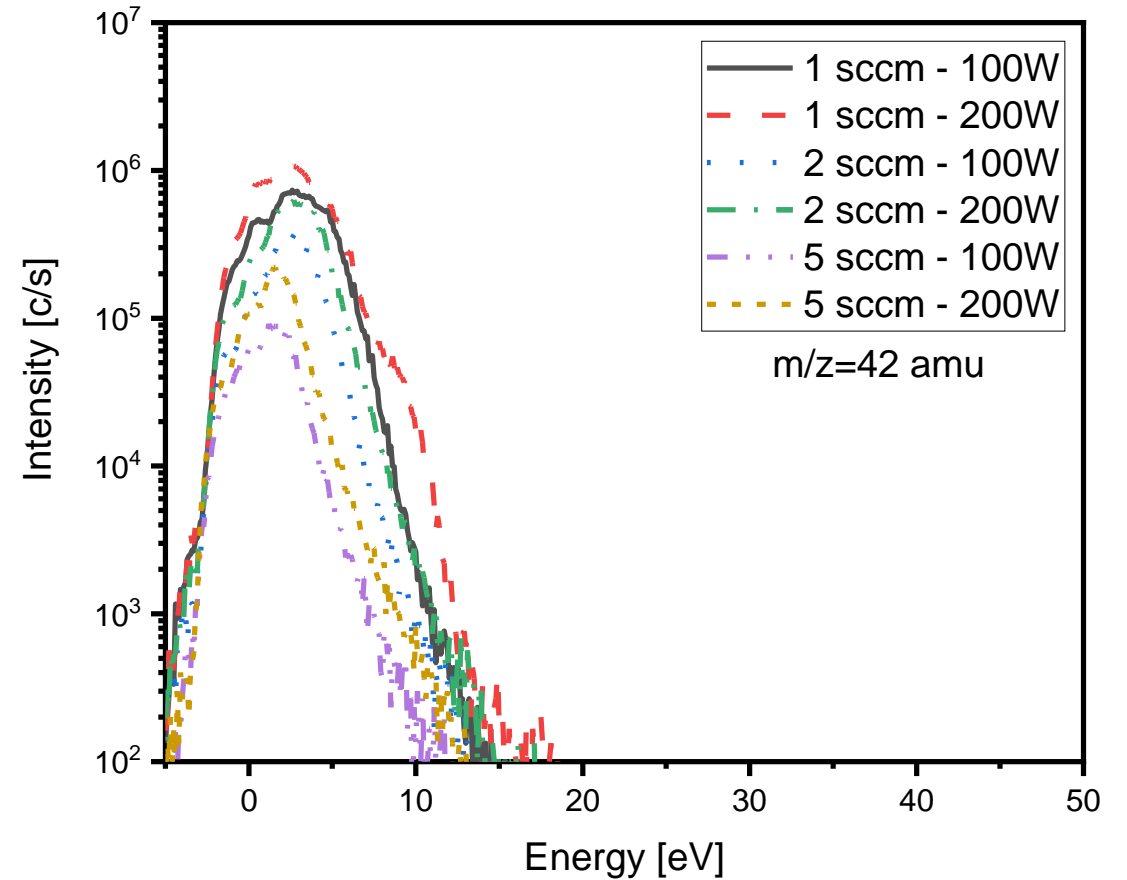
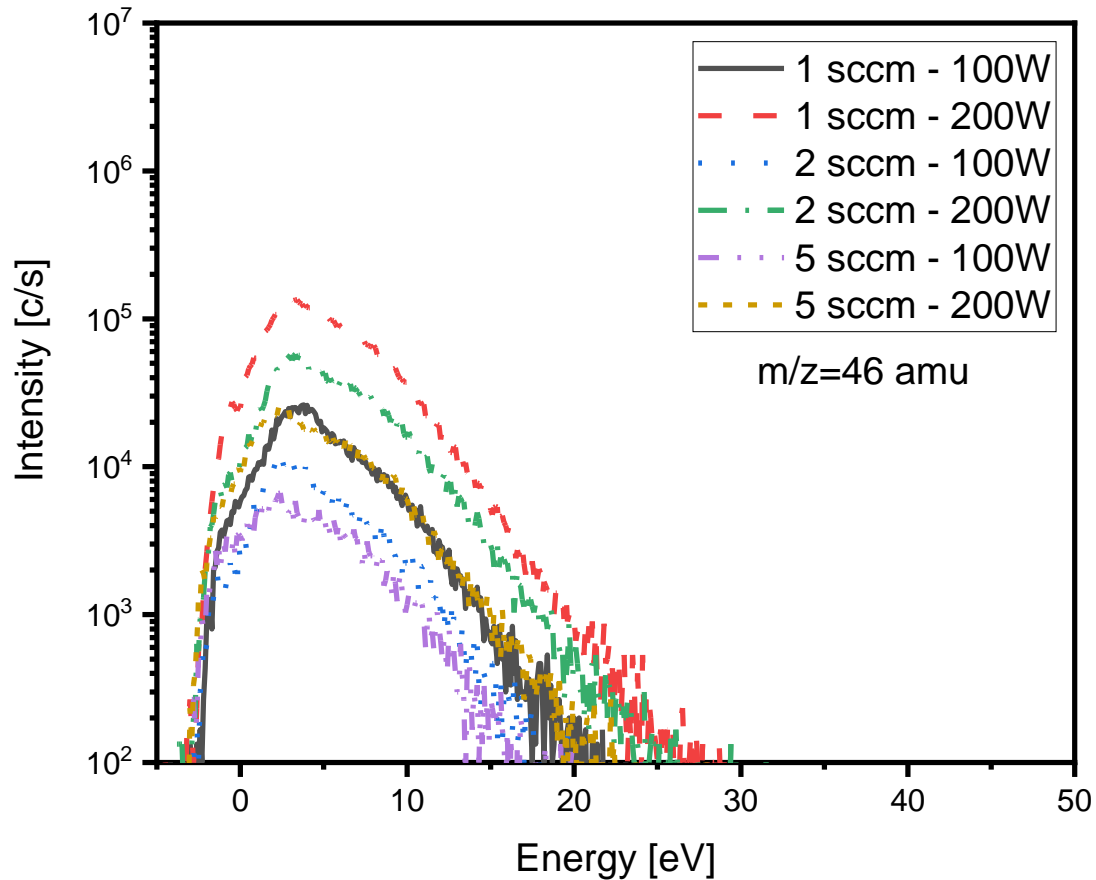
- Overlap of Nb^+ , Nb^0 , Kr^+ , N_2^+ and N_2^0 lines
- Increase of flow rate promote N_2^+ and N_2^0
- Impact on Nb^+ and Nb^0 lines intensity also observed by mass spectrometry



Investigation of NbN: IEDF of Nb⁺ and Kr⁺

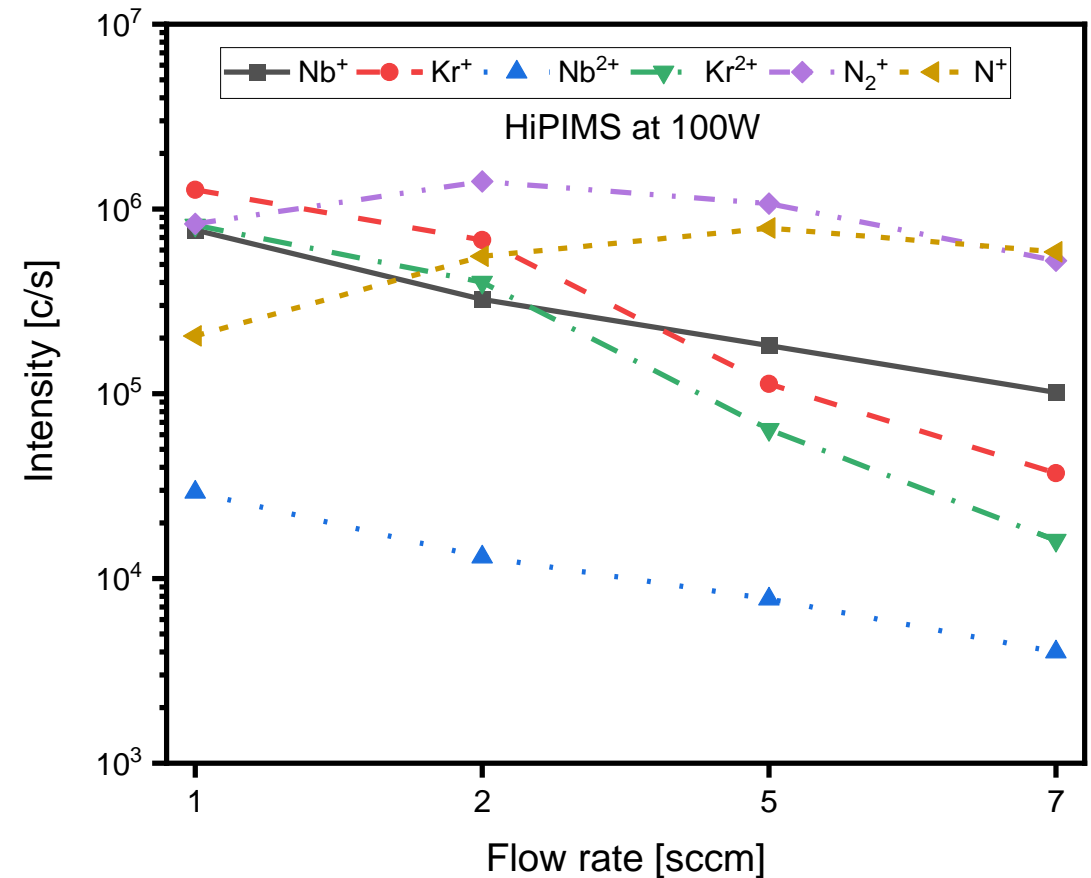


Investigation of NbN: IEDF of Nb²⁺ and Kr²⁺



Investigation of NbN: summary

- N_2 flow rate plays a crucial role for the formation of NbN
- Similar studies using Ar or Kr reported that low flow rate was favoured for the production of NbN thin films
- Increase of N_2 , reduces ion intensity and peak energy
- Correlation between flow rate and power



Future work

- Deposition of NbN on Cu samples using results obtained. Focus mainly on HiPIMS and bipolar HiPIMS
- Investigation of NbTiN using similar parameters as NbN
- Investigation on other HiPIMS properties to improve film quality
- Complementary investigation using Langmuir probe to get plasma properties

Acknowledgements

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